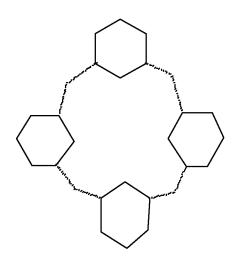
***** QUERY RESULTS ***** (STRUCTURE SEARCH - COMPOUND ON CLAIM 43 & 46)

=> d his 121

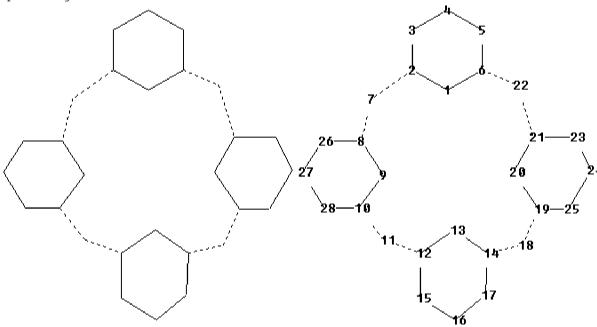
=> d que 121

L3 STR



Structure attributes must be viewed using STN Express query preparation:

Uploading L2.str



ring nodes :

```
ring bonds :
1-2 \quad 1-6 \quad 2-3 \quad 2-7 \quad 3-4 \quad 4-5 \quad 5-6 \quad 6-22 \quad 7-8 \quad 8-9 \quad 8-26 \quad 9-10 \quad 10-11 \quad 10-28 \quad 11-12
12 - 13 \quad 12 - 15 \quad 13 - 14 \quad 14 - 17 \quad 14 - 18 \quad 15 - 16 \quad 16 - 17 \quad 18 - 19 \quad 19 - 20 \quad 19 - 25 \quad 20 - 21 \quad 21 - 22
21-23 23-24
24-25 26-27 27-28
exact/norm bonds :
2-7 6-22 7-8 10-11 11-12 14-18 18-19 21-22
normalized bonds :
1-2 \quad 1-6 \quad 2-3 \quad 3-4 \quad 4-5 \quad 5-6 \quad 8-9 \quad 8-26 \quad 9-10 \quad 10-28 \quad 12-13 \quad 12-15 \quad 13-14 \quad 14-17
15-16 16-17 19-20 19-25 20-21 21-23 23-24 24-25 26-27 27-28
isolated ring systems :
containing 1 :
Match level:
1:Atom 2:Atom 3:Atom 4:Atom 5:Atom 6:Atom 7:Atom 8:Atom 9:Atom 10:Atom
11:Atom 12:Atom 13:Atom 14:Atom 15:Atom 16:Atom 17:Atom 18:Atom 19:Atom
20:Atom 21:Atom
22:Atom 23:Atom 24:Atom 25:Atom 26:Atom 27:Atom 28:Atom
           17874 SEA FILE=REGISTRY SSS FUL L3
L5
                  QUE ABB=ON PLU=ON RESIST OR RESIST# OR PHOTORESIST? OR
L10
                   PHOTO (2A) RESIST?
L16
                  STR
Structure attributes must be viewed using STN Express query preparation:
Uploading L3.str
                                                    17
chain nodes :
1 2 3 4 5 6 7 8 9 10 11 16 17
chain bonds :
1-2 \quad 1-8 \quad 2-3 \quad 3-4 \quad 4-5 \quad 5-6 \quad 5-7 \quad 8-9 \quad 9-10 \quad 10-11 \quad 11-16 \quad 11-17
exact/norm bonds :
2-3 3-4 4-5 5-6 5-7 8-9 9-10 10-11 11-16 11-17
exact bonds :
1-2 1-8
Match level:
1:Atom 2:CLASS 3:Atom 4:CLASS 5:CLASS 6:CLASS 7:CLASS 8:CLASS 9:Atom
10:CLASS
11:CLASS 16:CLASS 17:CLASS
```

Generic attributes :

3:

Saturation : Unsaturated 9:

Saturation : Unsaturated

L18 2 SEA FILE=REGISTRY SUB=L5 SSS FUL L16 L19 2 SEA FILE=HCAPLUS ABB=ON PLU=ON L18

L21 2 SEA FILE=HCAPLUS ABB=ON PLU=ON L19 AND L10

=> d 121 1-2 ibib abs hitstr hitind

L21 ANSWER 1 OF 2 HCAPLUS COPYRIGHT 2009 ACS on STN ACCESSION NUMBER: 2008:534110 HCAPLUS Full-text

DOCUMENT NUMBER: 149:115490

TITLE: Calix[4]resorcinarene derivatives as high-resolution

resist materials for supercritical CO2

processing

AUTHOR(S): Felix, Nelson M.; De Silva, Anuja; Ober, Christopher

Κ.

CORPORATE SOURCE: School of Chemical and Biomolecular Engineering,

Cornell University, Ithaca, NY, 14853, USA

SOURCE: Advanced Materials (Weinheim, Germany) (2008), 20(7),

1303-1309

CODEN: ADVMEW; ISSN: 0935-9648 Wiley-VCH Verlag GmbH & Co. KGAA

DOCUMENT TYPE: Journal LANGUAGE: English

AB Ultra-high-resolution lithog. resists based on calix[4]resorcinarene derivs. are shown to be compatible with supercrit. CO2 processing upon the incorporation of specific functionalities, as illustrated by the inset to the figure. The compds. show high glass-transition temps., excellent solubility in supercrit. CO2, and good film forming properties, enabling the patterning of line/space features as small as 70 nm (depicted in the figure).

IT 623159-14-8

PUBLISHER:

RL: PEP (Physical, engineering or chemical process); PRP (Properties); PROC (Process)

(calix[4]resorcinarene derivs. as high-resolution resist materials for supercrit. CO2 processing)

RN 623159-14-8 HCAPLUS

```
CC 74-5 (Radiation Chemistry, Photochemistry, and Photographic and Other Reprographic Processes)
```

ST calix resorcinarene deriv high resoln resist supercrit carbon dioxide

IT Photoresists

(calix[4]resorcinarene derivs. as high-resolution resist materials for supercrit. CO2 processing)

IT 124-38-9, Carbon dioxide, uses

RL: NUU (Other use, unclassified); USES (Uses)

(calix[4]resorcinarene derivs. as high-resolution resist

materials for supercrit. CO2 processing)

IT 65338-98-9 129831-85-2 176897-13-5 181231-12-9 250715-31-2

6231.59~14~8 649720-85-4 929207-68-1 929209-81-4

1034474-84-4 1034474-85-5 1034474-86-6

RL: PEP (Physical, engineering or chemical process); PRP (Properties); PROC (Process)

(calix[4]resorcinarene derivs. as high-resolution resist materials for supercrit. CO2 processing)

IT 1034474-83-3P 1034474-87-7P

RL: PEP (Physical, engineering or chemical process); PRP (Properties); SPN (Synthetic preparation); PREP (Preparation); PROC (Process)

(calix[4]resorcinarene derivs. as high-resolution resist

materials for supercrit. CO2 processing)

REFERENCE COUNT: 36 THERE ARE 36 CITED REFERENCES AVAILABLE FOR THIS RECORD. ALL CITATIONS AVAILABLE IN THE RE FORMAT

L21 ANSWER 2 OF 2 HCAPLUS COPYRIGHT 2009 ACS on STN ACCESSION NUMBER: 2003:879781 HCAPLUS $\underline{\text{Full-text}}$

DOCUMENT NUMBER: 139:388462

TITLE: tert-Butoxycarbonylalkoxycalixresorcinarenes having

high solubility in casting solvents and radiation-sensitive positive resists

containing the same

INVENTOR(S): Nishikubo, Tadaomi; Kudo, Hiroto PATENT ASSIGNEE(S): JSR Ltd., Japan; Kanagawa University

SOURCE: Jpn. Kokai Tokkyo Koho, 18 pp.

CODEN: JKXXAF

DOCUMENT TYPE: Patent LANGUAGE: Japanese

FAMILY ACC. NUM. COUNT: 1

PATENT INFORMATION:

PATENT NO.	KIND	DATE	APPLICATION NO.	DATE
JP 2003321423	A	20031111	JP 2002-133996	20020509
JP 4076789	B2	20080416		
PRIORITY APPLN. INFO.:			JP 2002-133996	20020509
OTHER SOURCE(S):	MARPAT	139:388462		
GI				

$$P = \frac{R^2}{CH_3} O - (CH_2)_p - C - O - C - CH_3$$
 CH_3
 CH_3

- AB The compds. I (R1 = C1-18 alkyl, P; R2 = H, C1-15 alkoxy; m, p = 0-2; n = 4-12) and resists containing I and radiation-sensitive acid generators are septilized. The resists produce high-resolution patterns for fabrication of integrated circuits.
- IT 623159-14-8P 623159-15-9P

RL: IMF (Industrial manufacture); TEM (Technical or engineered material use); PREP (Preparation); USES (Uses)

(tert-butoxycarbonylalkoxycalixresorcinarenes having high solvent solubility

for liable pos.-working radiation-sensitive resists)

- RN 623159-14-8 HCAPLUS

RN 623159-15-9 HCAPLUS

CN Carbonic acid, 2,8,14,20-tetrakis[4-[[(1,1-dimethylethoxy)carbonyl]oxy]-3-ethoxyphenyl]pentacyclo[19.3.1.13,7.19,13.115,19]octacosa-1(25),3,5,7(28),9,11,13(27),15,17,19(26),21,23-dodecaene-4,6,10,12,16,18,22,24-octayl octakis(1,1-dimethylethyl) ester (9CI) (CA INDEX NAME)

PAGE 1-A

PAGE 2-A

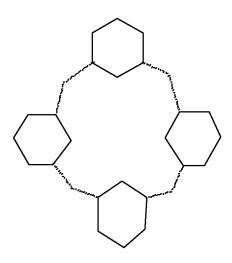
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ICM C07C069-712
IC
     ICS C08G061-02; G03F007-039; H01L021-027
CC
     74-5 (Radiation Chemistry, Photochemistry, and Photographic and Other
     Reprographic Processes)
     Section cross-reference(s): 25
ST
     butoxycarbonylalkoxy calixresorcinarene chem amplified pos
     photoresist; radiation sensitive resist
     butoxycarbonylalkoxy calixresorcinarene solvent solv
ΙT
     Metacyclophanes
     RL: IMF (Industrial manufacture); TEM (Technical or engineered material
     use); PREP (Preparation); USES (Uses)
        (calixarenes; tert-butoxycarbonylalkoxycalixresorcinarenes having high
        solvent solubility for liable pos.-working radiation-sensitive
       resists)
ΙT
     Resists
        (radiation-sensitive; tert-butoxycarbonylalkoxycalixresorcinarenes
        having high solvent solubility for liable pos.-working radiation-sensitive
        resists)
ΙT
     Positive photoresists
        (tert-butoxycarbonylalkoxycalixresorcinarenes having high solvent
solubility
        for liable pos.-working radiation-sensitive resists)
     74227-35-3
ΤТ
     RL: CAT (Catalyst use); TEM (Technical or engineered material use); USES
     (Uses)
        (acid generators; tert-butoxycarbonylalkoxycalixresorcinarenes having
        high solvent solubility for liable pos.-working radiation-sensitive
       resists)
                 176897-13-5P 182370-80-5P 203714-14-1P
     65338-98-9P
                                                               623159-00-2P
ΤТ
     623159-02-4P
                  623159-03-5P
     RL: IMF (Industrial manufacture); RCT (Reactant); PREP (Preparation); RACT
     (Reactant or reagent)
        (tert-butoxycarbonylalkoxycalixresorcinarenes having high solvent
solubility
        for liable pos.-working radiation-sensitive resists)
     623159-05-7P
                  623159-06-8P
                                  623159-07-9P
                                                 623159-08-0P
                   623159-13-7P 623159-14-8P 623159-15-9P
     623159-12-6P
     RL: IMF (Industrial manufacture); TEM (Technical or engineered material
     use); PREP (Preparation); USES (Uses)
        (tert-butoxycarbonylalkoxycalixresorcinarenes having high solvent
solubility
        for liable pos.-working radiation-sensitive resists)
    108-46-3, Resorcinol, reactions 112-44-7, Undecanal 121-32-4,
     Ethylvanillin 123-08-0, p-Hydroxybenzaldehyde 123-63-7 629-76-5,
     Pentadecanol 629-90-3, Heptadecanal 1454-85-9, 1-Heptadecanol
                             5292-43-3, Tert-Butyl bromoacetate 10486-19-8,
     2765-11-9, Pentadecanal
     Tridecanal 24424-99-5, Di-tert-butyl dicarbonate
     RL: RCT (Reactant); RACT (Reactant or reagent)
        (tert-butoxycarbonylalkoxycalixresorcinarenes having high solvent
        for liable pos.-working radiation-sensitive resists)
```

***** QUERY RESULTS ***** (STRUCTURE AND TEXT SEARCH - COMPOUND IN CLAIM 43 & 46)

=> d his 122

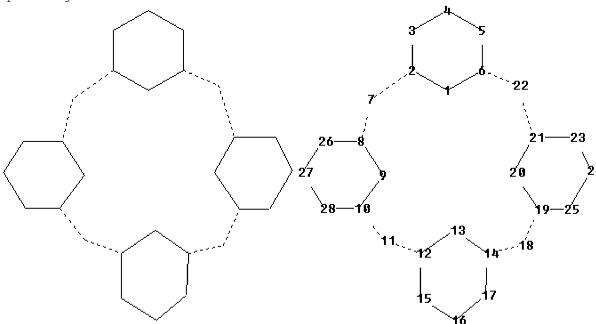
=> d que 122

L3 STR



Structure attributes must be viewed using STN Express query preparation:

Uploading L2.str



ring nodes :

```
1 2 3 4 5 6 7 8 9 10 11 12 13 14 15 16 17 18 19 20 21 22 23 24 25 26 27 28 ring bonds:

1-2 1-6 2-3 2-7 3-4 4-5 5-6 6-22 7-8 8-9 8-26 9-10 10-11 10-28 11-12 12-13 12-15 13-14 14-17 14-18 15-16 16-17 18-19 19-20 19-25 20-21 21-22 21-23 23-24 24-25 26-27 27-28 exact/norm bonds:

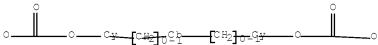
2-7 6-22 7-8 10-11 11-12 14-18 18-19 21-22 normalized bonds:

1-2 1-6 2-3 3-4 4-5 5-6 8-9 8-26 9-10 10-28 12-13 12-15 13-14 14-17 15-16 16-17 19-20 19-25 20-21 21-23 23-24 24-25 26-27 27-28 isolated ring systems: containing 1:
```

Match level:

1:Atom 2:Atom 3:Atom 4:Atom 5:Atom 6:Atom 7:Atom 8:Atom 9:Atom 10:Atom 11:Atom 12:Atom 13:Atom 14:Atom 15:Atom 16:Atom 17:Atom 18:Atom 19:Atom 20:Atom 21:Atom 23:Atom 24:Atom 25:Atom 26:Atom 27:Atom 28:Atom

```
L5
         17874 SEA FILE=REGISTRY SSS FUL L3
          6250 SEA FILE=HCAPLUS ABB=ON PLU=ON L5
L9
L10
               QUE ABB=ON PLU=ON RESIST OR RESIST# OR PHOTORESIST? OR
                PHOTO (2A) RESIST?
L11
            89 SEA FILE=HCAPLUS ABB=ON PLU=ON L9 (L) L10
L12
          3317 SEA FILE=HCAPLUS ABB=ON PLU=ON L9 (L) PREP+ALL/RL
          3706 SEA FILE=HCAPLUS ABB=ON PLU=ON L9 (L) RACT/RL
L13
            33 SEA FILE=HCAPLUS ABB=ON PLU=ON L11 AND L12 AND L13
L14
L15
            21 SEA FILE=HCAPLUS ABB=ON PLU=ON L14 AND (AY<2006 OR PY<2006
               OR PRY<2006)
L16
               STR
```



Structure attributes must be viewed using STN Express query preparation:

```
chain nodes :
1  2  3  4  5  6  7  8  9  10  11  16  17
chain bonds :
1-2  1-8  2-3  3-4  4-5  5-6  5-7  8-9  9-10  10-11  11-16  11-17
exact/norm bonds :
2-3  3-4  4-5  5-6  5-7  8-9  9-10  10-11  11-16  11-17
exact bonds :
1-2  1-8
```

Match level:

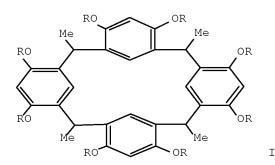
PRIORITY APPLN. INFO.:

1:Atom 2:CLASS 3:Atom 4:CLASS 5:CLASS 6:CLASS 7:CLASS 8:CLASS 9:Atom 10:CLASS 11:CLASS 16:CLASS 17:CLASS Generic attributes : : Unsaturated 9: Saturation : Unsaturated 2 SEA FILE=REGISTRY SUB=L5 SSS FUL L16 T.18 2 SEA FILE=HCAPLUS ABB=ON PLU=ON L18 L19 21 SEA FILE=HCAPLUS ABB=ON PLU=ON L15 AND L10 L20 2 SEA FILE=HCAPLUS ABB=ON PLU=ON L19 AND L10 L21 20 SEA FILE=HCAPLUS ABB=ON PLU=ON L20 NOT L21 L22 => d 122 1-20 ibib abs hitstr hitind L22 ANSWER 1 OF 20 HCAPLUS COPYRIGHT 2009 ACS on STN ACCESSION NUMBER: 2005:1123873 HCAPLUS Full-text DOCUMENT NUMBER: 143:413494 TITLE: Calixresorcinarene compounds, photoresist base materials, and compositions thereof INVENTOR(S): Ishii, Hirotoshi; Owada, Takanori; Shibasaki, Yuzi; Ueda, Mitsuru PATENT ASSIGNEE(S): Idemitsu Kosan Co., Ltd., Japan SOURCE: PCT Int. Appl., 52 pp. CODEN: PIXXD2 DOCUMENT TYPE: Patent LANGUAGE: Japanese FAMILY ACC. NUM. COUNT: 1 PATENT INFORMATION: PATENT NO. KIND DATE APPLICATION NO. DATE WO 2005097725 A1 2005 _____ A1 20051020 WO 2005-JP6512 20050401 <--W: AE, AG, AL, AM, AT, AU, AZ, BA, BB, BG, BR, BW, BY, BZ, CA, CH, CN, CO, CR, CU, CZ, DE, DK, DM, DZ, EC, EE, EG, ES, FI, GB, GD, GE, GH, GM, HR, HU, ID, IL, IN, IS, JP, KE, KG, KP, KR, KZ, LC, LK, LR, LS, LT, LU, LV, MA, MD, MG, MK, MN, MW, MX, MZ, NA, NI, NO, NZ, OM, PG, PH, PL, PT, RO, RU, SC, SD, SE, SG, SK, SL, SM, SY, TJ, TM, TN, TR, TT, TZ, UA, UG, US, UZ, VC, VN, YU, ZA, ZM, ZW RW: BW, GH, GM, KE, LS, MW, MZ, NA, SD, SL, SZ, TZ, UG, ZM, ZW, AM, AZ, BY, KG, KZ, MD, RU, TJ, TM, AT, BE, BG, CH, CY, CZ, DE, DK, EE, ES, FI, FR, GB, GR, HU, IE, IS, IT, LT, LU, MC, NL, PL, PT, RO, SE, SI, SK, TR, BF, BJ, CF, CG, CI, CM, GA, GN, GQ, GW, ML, MR, NE, SN, TD, TG EP 1734032 20061220 EP 2005-728046 20050401 <--A1 R: BE, DE, FR, GB CN 1938259 A 20070328 CN 2005-80010812 20050401 <--US 20070190451 A1 20070816 US 2006-594282 20060926 <-KR 2007003980 A 20070105 KR 2006-720033 20060927 <-RITY APPLN. INFO.: JP 2004-111459 A 20040405 <--

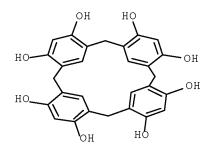
JP 2004-111460 A 20040405 <--WO 2005-JP6512 W 20050401 <--

OTHER SOURCE(S): MARPAT 143:413494

GΙ



- Disclosed are calixresorcinarene compds. (I: wherein R = h, 1-tetrahydropyranyl, 1-tetrahydrofuranyl, organic moiety having 2-methyl-2-adamantyloxycarbonylmethyl groups, etc.), use of I as resist base material, and resist compns. containing I. The compds. are useful for nanofabrication with extreme UV rays or electron beam.
- IT 125748-07-4DP, reaction products with bromoacetic acid esters RL: SPN (Synthetic preparation); TEM (Technical or engineered material use); PREP (Preparation); USES (Uses) (synthesis and use as radiation resists for nano-fabrication)
- RN 125748-07-4 HCAPLUS
- CN Pentacyclo[19.3.1.13,7.19,13.115,19]octacosa-1(25),3,5,7(28),9,11,13(27),15,17,19(26),21,23-dodecaene-4,6,10,12,16,18,22,24-octol (CA INDEX NAME)



IT 125748-07-4P

RL: RCT (Reactant); SPN (Synthetic preparation); PREF (Preparation); RACT (Reactant or reagent)

(synthesis and use for radiation resist base materials)

- RN 125748-07-4 HCAPLUS
- CN Pentacyclo[19.3.1.13,7.19,13.115,19]octacosa-1(25),3,5,7(28),9,11,13(27),15,17,19(26),21,23-dodecaene-4,6,10,12,16,18,22,24-octol (CA INDEX NAME)

$$HO$$
 OH
 HO
 OH
 OH

IC ICM C07C067-31

ICS C07C069-712; G03F007-039; H01L021-027

CC 74-5 (Radiation Chemistry, Photochemistry, and Photographic and Other Reprographic Processes)
Section cross-reference(s): 23

calixresorcinarene deriv radiation resist nanofabrication

IT Photoresists

ST

(UV; calixresorcinarene derivs. for resist base materials for nano-fabrication)

IT Electron beam resists

(calixresorcinarene derivs. for $x \approx sist$ base materials for nano-fabrication)

IT Lithography

(submicron; radiation resist composition containing calixresorcinarene derivs. for)

IT 280-57-9, 1,4-Diazabicyclo[2.2.2]octane 66003-78-9

RL: TEM (Technical or engineered material use); USES (Uses) (radiation resist composition containing calixresorcinarene derivs. and)

IT 108-46-3, Resorcinol, reactions

RL: RCT (Reactant); RACT (Reactant or reagent) (reaction with acetaldehyde in synthesis of calixresorcinarene derivs. for radiation resist)

IT 75-07-0, Acetaldehyde, reactions

RL: RCT (Reactant); RACT (Reactant or reagent)
(reaction with resorcinol in synthesis of calixresorcinarene derivs.
for radiation resist)

IT 5292-43-3DP, tert-Butyl bromoacetate, reaction product with calixresorcinarene 125748-07-4DP, reaction products with bromoacetic acid esters 625122-37-4DP, reaction product with calixresorcinarene

RL: SPN (Synthetic preparation); TEM (Technical or engineered material use); PREP (Preparation); USES (Uses)

(synthesis and use as radiation resists for nano-fabrication)

IT 125748-07-4P

RL: RCT (Reactant); SPN (Synthetic preparation); PREP (Preparation); RACT (Reactant or reagent)

(synthesis and use for radiation resist base materials)

REFERENCE COUNT: 4 THERE ARE 4 CITED REFERENCES AVAILABLE FOR THIS RECORD. ALL CITATIONS AVAILABLE IN THE RE FORMAT

L22 ANSWER 2 OF 20 HCAPLUS COPYRIGHT 2009 ACS on STN ACCESSION NUMBER: 2005:563698 HCAPLUS Full-text

DOCUMENT NUMBER: 143:106359

TITLE: Acid-labile acetal group-containing

calix[4]resorcinarenes and chemically amplified

resists containing them

INVENTOR(S): Nishikubo, Tadaomi; Kudo, Hiroto PATENT ASSIGNEE(S): JSR Ltd., Japan; Kanagawa University

SOURCE: Jpn. Kokai Tokkyo Koho, 16 pp.

CODEN: JKXXAF

DOCUMENT TYPE: Patent LANGUAGE: Japanese

FAMILY ACC. NUM. COUNT: 1

PATENT INFORMATION:

PATENT NO.	KIND	DATE	APPLICATION NO.	DATE
JP 2005170902	A	20050630	JP 2003-416509	20031215 <
PRIORITY APPLN. INFO.:			JP 2003-416509	20031215 <
GI				

$$H_3C$$
 O H_2 O H_2 O H_3 H_4 H_4 H_4 H_4 H_5 H_4 H_5 H_4 H_5 H_5 H_6 H_6 H_7 H_8 H_8

AB The calix[4]resorcinarenes are I (R = Me, 4-MeOCH2O2CCH2OC6H4). The resists contain I and photoacid generators. The I show good solubility in casting solvents, and good resistance to heat and alkali developers, resulting in forming high-resolution patterns.

Ι

IT 65338-98-9P 130508-38-2P 171799-35-2P 176897-13-5P 710970-56-2P 830329-32-3P

DI MAN (M.) ' ' 1 C () DOT (D.)

RL: IMF (Industrial manufacture); RCT (Reactant); PREP

(Preparation); RACT (Reactant or reagent)

(acid-labile acetal group-containing calixresorcinarenes for chemical
amplified resists)

RN 65338-98-9 HCAPLUS

CN Pentacyclo[19.3.1.13,7.19,13.115,19]octacosa-1(25),3,5,7(28),9,11,13(27),15,17,19(26),21,23-dodecaene-4,6,10,12,16,18,22,24-octol, 2,8,14,20-tetramethyl- (CA INDEX NAME)

RN 130508-38-2 HCAPLUS

RN 171799-35-2 HCAPLUS

RN 176897-13-5 HCAPLUS

CN Pentacyclo[19.3.1.13,7.19,13.115,19]octacosa-1(25),3,5,7(28),9,11,13(27),15,17,19(26),21,23-dodecaene-4,6,10,12,16,18,22,24-octol, 2,8,14,20-tetrakis(4-hydroxyphenyl)- (CA INDEX NAME)

RN 710970-56-2 HCAPLUS

PAGE 1-A

HO2C-CH2-O-CH2-CO2H
HO2C-CH2-O-CH2-CO2H
HO2C-CH2-O-CH2-CO2H
CH2-CO2H

RN 830329-32-3 HCAPLUS

PAGE 1-A

PAGE 2-A

PAGE 3-A

IT 830329-30-1P 830329-31-2P

RL: IMF (Industrial manufacture); TEM (Technical or engineered material use); PREP (Preparation); USES (Uses)

(acid-labile acetal group-containing calixresorcinarenes for chemical
amplified resists)

RN 830329-30-1 HCAPLUS

1(25),3,5,7(28),9,11,13(27),15,17,19(26),21,23-dodecaene-4,6,10,12,16,18,22,24-octayl)octakis(oxy)]octakis-, octakis(methoxymethyl) ester (9CI) (CA INDEX NAME)

RN 830329-31-2 HCAPLUS
CN Acetic acid, 2,2',2'',2''',2'''',2'''',2''''',2''''',2'''''-[[2,8,14,20-tetrakis[4-[2-(methoxymethoxy)-2-oxoethoxy]phenyl]pentacyclo[19.3.1.13,7.19,13.115,19]octacosa-1(25),3,5,7(28),9,11,13(27),15,17,19(26),21,23-dodecaene-4,6,10,12,16,18,22,24-octayl]octakis(oxy)]octakis-, octakis(methoxymethyl) ester (9CI) (CA INDEX NAME)

PAGE 2-A

IC ICM C07C069-736

ICS G03F007-039; H01L021-027

CC 74-5 (Radiation Chemistry, Photochemistry, and Photographic and Other Reprographic Processes)

Section cross-reference(s): 25

ST acetal calixresorcinarene chem amplified resist

ΤТ Resists

> (radiation-sensitive; acid-labile acetal group-containing calixresorcinarenes for chemical amplified resists)

65338-98-9P 130508-38-2P 171799-35-2P ΤТ

176897-13-5P 710970-56-2P 830329-32-3P

RL: IMF (Industrial manufacture); RCT (Reactant); PREP

(Preparation); RACT (Reactant or reagent)

(acid-labile acetal group-containing calixresorcinarenes for chemical amplified resists)

830329-30-1P 830329-31-2P TT

> RL: IMF (Industrial manufacture); TEM (Technical or engineered material use); PREP (Preparation); USES (Uses)

(acid-labile acetal group-containing calixresorcinarenes for chemical amplified resists)

105-36-2, Ethyl bromoacetate 107-30-2, Chloromethyl methyl ether 108-46-3, Resorcinol, reactions 123-08-0, p-Hydroxybenzaldehyde 123-63-7

RL: RCT (Reactant); RACT (Reactant or reagent) (acid-labile acetal group-containing calixresorcinarenes for chemical amplified resists)

L22 ANSWER 3 OF 20 HCAPLUS COPYRIGHT 2009 ACS on STN ACCESSION NUMBER: 2005:253630 HCAPLUS Full-text

DOCUMENT NUMBER: 142:345148

TITLE: Photoresist, its purification and

photoresist composition showing improved

sensitivity, contrast, and line-edge-roughness to

extreme UV

Ueda, Mitsuru; Ishii, Hirohisa INVENTOR(S): PATENT ASSIGNEE(S): Idemitsu Kosan Co., Ltd., Japan SOURCE: Jpn. Kokai Tokkyo Koho, 32 pp.

CODEN: JKXXAF

DOCUMENT TYPE: Patent Japanese LANGUAGE:

FAMILY ACC. NUM. COUNT: 1

PATENT INFORMATION:

PATENT NO.	KIND	DATE	APPLICATION NO.	DATE
JP 2005075767	A	20050324	JP 2003-307443	20030829 <

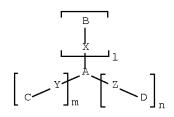
PRIORITY APPLN. INFO.:

JP 2003-307443

20030829 <--

OTHER SOURCE(S):
GI

E(S): MARPAT 142:345148



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- The title photoresist comprises an extreme UV light-reactive organic compound represented by I (A = C1-50-aliphatic, C6-50-aromatic, etc.; B, C, D = extreme UV light-reactive group-containing C1-50-aliphatic, C6-50-aromatic, etc.; X, Y, Z = single bond, ether linkage; l, m, n = 0-5) and \leq 10 ppm of basic impurities. The chemical amplified photoresist composition is sensitive to extreme UV and electron beam.
- IT 65338-98-9P

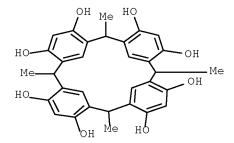
RL: RCT (Reactant); SPN (Synthetic preparation); PREP

(Preparation); RACT (Reactant or reagent)

(photoresist preparation; photoresist, its purification and photoresist composition showing improved sensitivity, contrast, and line-edge-roughness to extreme UV)

RN 65338-98-9 HCAPLUS

CN Pentacyclo[19.3.1.13,7.19,13.115,19]octacosa-1(25),3,5,7(28),9,11,13(27),15,17,19(26),21,23-dodecaene-4,6,10,12,16,18,22,24-octol, 2,8,14,20-tetramethyl- (CA INDEX NAME)



IT 65338-98-9DP, reaction product with tert-Butylbromoacetate RL: SPN (Synthetic preparation); TEM (Technical or engineered material use); PREP (Preparation); USES (Uses)

(photoresist preparation; photoresist, its purification and photoresist composition showing improved sensitivity, contrast, and line-edge-roughness to extreme UV)

RN 65338-98-9 HCAPLUS

CN Pentacyclo[19.3.1.13,7.19,13.115,19]octacosa-1(25),3,5,7(28),9,11,13(27),15,17,19(26),21,23-dodecaene-4,6,10,12,16,18,22,24-octol, 2,8,14,20-tetramethyl- (CA INDEX NAME)

IC ICM C07C069-736

ICS C07C067-56; G03F007-004; G03F007-039; H01L021-027

CC 74-5 (Radiation Chemistry, Photochemistry, and Photographic and Other Reprographic Processes)
Section cross-reference(s): 38, 73, 76

ST photoresist purifn compn extreme UV lithog

IT Photoresists

(photoresist, its purification and photoresist composition showing improved sensitivity, contrast, and line-edge-roughness to extreme UV)

IT 282713-83-1

RL: CAT (Catalyst use); USES (Uses)

(photoacid generator; photoresist, its purification and photoresist composition showing improved sensitivity, contrast, and line-edge-roughness to extreme UV)

IT 75-07-0, Acetaldehyde, reactions 108-46-3, Resorcinol, reactions 5292-43-3D, tert-Butylbromoacetate, reaction products with C-Methylcalix[4]resorcinarene.

RL: RCT (Reactant); RACT (Reactant or reagent)
(photoresist preparation; photoresist, its purification and
photoresist composition showing improved sensitivity, contrast, and
line-edge-roughness to extreme UV)

IT 65338-98-9P

RL: RCT (Reactant); SPN (Synthetic preparation); PREP

(Preparation); RACT (Reactant or reagent)

(photoresist preparation; photoresist, its purification and photoresist composition showing improved sensitivity, contrast, and line-edge-roughness to extreme UV)

IT 65338-98-9DP, reaction product with tert-Butylbromoacetate RL: SPN (Synthetic preparation); TEM (Technical or engineered material use); PREP (Preparation); USES (Uses)

(photoresist preparation; photoresist, its purification and photoresist composition showing improved sensitivity, contrast, and line-edge-roughness to extreme UV)

IT 24203-36-9, Potassium ion, processes

RL: REM (Removal or disposal); PROC (Process)
(photoresist, its purification and photoresist composition
showing improved sensitivity, contrast, and line-edge-roughness to
extreme UV)

L22 ANSWER 4 OF 20 HCAPLUS COPYRIGHT 2009 ACS on STN ACCESSION NUMBER: 2004:1038016 HCAPLUS <u>Full-text</u>

DOCUMENT NUMBER: 142:165419

TITLE: Synthesis of novel chemically amplified materials

based on calix[4]arene derivatives with acetal

moieties

AUTHOR(S): Kudo, Hiroto; Mitani, Kouji; Koyama, Syuhei;

Nishikubo, Tadatomi

CORPORATE SOURCE: Department of Applied Chemistry, Faculty of

Engineering, Kanagawa University, Yokohama, 221-8686,

Japan

SOURCE: Bulletin of the Chemical Society of Japan (

2004), 77(11), 2109-2114

CODEN: BCSJA8; ISSN: 0009-2673

PUBLISHER: Chemical Society of Japan

DOCUMENT TYPE: Journal LANGUAGE: English

OTHER SOURCE(S): CASREACT 142:165419

AB The synthesis and photoinduced deprotection reaction of calix[4]resorcinarene derivs. with pendant acetal moieties were examined C-methyl[(methoxymethylcarbonyl)oxy]calix[4]resorcinarene (CRA-Acetal) and C-4-

hydroxyphenyl[(methoxymethylcarbonyl)oxy]calix[4]resorcinarene (CRAph-Acetal) were prepared from C-methylcalix[4]resorcinarene (CRA) and C-4-hydroxyphenylcalix[4]resorcinarene (CRAph). The synthesized CRA-Acetal and

CRAph-Acetal had good solubilities, good film-forming properties, and high thermal stabilities. The photoinduced deprotection reaction of CRA-Acetal and CRAph-Acetal was examined in the presence of bis[4-

(diphenylsulfonio)phenyl]sulfide (DPSP) as a photoacid generator in the film state upon UV irradiation It was found that the deprotection reaction of acetal groups of CRA-Acetal and CRAph-Acetal proceeded smoothly without further heating to produce the corresponding calixarene derivs., CRA-COOH and CRAph-COOH with carboxylic acid groups.

IT 171799-35-2P 830329-32-3P

RL: PRP (Properties); RCT (Reactant); SPN (Synthetic preparation)

; PREP (Preparation); RACT (Reactant or reagent)

(hydrolysis in aqueous KOH solution)

RN 171799-35-2 HCAPLUS

NAME)

RN 830329-32-3 HCAPLUS

PAGE 1-A

PAGE 2-A

PAGE 3-A

RN 623159-12-6 HCAPLUS
CN Acetic acid, 2,2',2'',2''',2'''',2''''',2''''',2''''',2'''''-[[2,8,14,20-tetrakis[4-[2-(1,1-dimethylethoxy)-2-oxoethoxy]phenyl]pentacyclo[19.3.1.13,7.19,13.115,19]octacosa-1(25),3,5,7(28),9,11,13(27),15,17,19(26),21,23-dodecaene-4,6,10,12,16,18,22,24-octayl]octakis(oxy)]octakis-, octakis(1,1-dimethylethyl) ester (9CI) (CA INDEX NAME)

PAGE 1-A

PAGE 2-A

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IT 65338-98-9 176897-13-5

RL: PRP (Properties); RCT (Reactant); RACT (Reactant or reagent) (reaction with Et bromoacetate using K2CO3 in presence of TBAB as phase-transfer catalyst)

RN 65338-98-9 HCAPLUS

CN Pentacyclo[19.3.1.13,7.19,13.115,19]octacosa-1(25),3,5,7(28),9,11,13(27),15,17,19(26),21,23-dodecaene-4,6,10,12,16,18,22,24-octol, 2,8,14,20-tetramethyl- (CA INDEX NAME)

RN 176897-13-5 HCAPLUS

CN Pentacyclo[19.3.1.13,7.19,13.115,19]octacosa-1(25),3,5,7(28),9,11,13(27),15,17,19(26),21,23-dodecaene-4,6,10,12,16,18,22,24-octol, 2,8,14,20-tetrakis(4-hydroxyphenyl)- (CA INDEX NAME)

RN 710970-56-2 HCAPLUS
CN Acetic acid, 2,2',2'',2''',2'''',2'''',2''''',2''''',2'''''-[[2,8,14,20-tetrakis[4-(carboxymethoxy)phenyl]pentacyclo[19.3.1.13,7.19,13.115,19]octacosa-1(25),3,5,7(28),9,11,13(27),15,17,19(26),21,23-dodecene-4,6,10,12,16,18,22,24-octayl]octakis(oxy)]octakis- (CA INDEX NAME)

PAGE 1-A

PAGE 2-A

RN 830329-30-1 HCAPLUS

RN 830329-31-2 HCAPLUS

CN Acetic acid, 2,2',2'',2''',2'''',2'''',2''''',2''''',2'''''-[[2,8,14,20-tetrakis[4-[2-(methoxymethoxy)-2-oxoethoxy]phenyl]pentacyclo[19.3.1.13,7.19,13.115,19]octacosa-

1(25),3,5,7(28),9,11,13(27),15,17,19(26),21,23-dodecaene-4,6,10,12,16,18,22,24-octayl]octakis(oxy)]octakis-, octakis(methoxymethyl) ester (9CI) (CA INDEX NAME)

- CC 74-5 (Radiation Chemistry, Photochemistry, and Photographic and Other Reprographic Processes)
- ST synthesis photoinduced deprotection calixresorcinarene acetal deriv chem amplified photoresist
- IT Metacyclophanes
 RL: CPS (Chemical process); PEP (Physical, engineering or chemical
 process); PRP (Properties); RCT (Reactant); SPN (Synthetic preparation);

PREP (Preparation); PROC (Process); RACT (Reactant or reagent)
(calixarenes; synthesis and photoinduced deprotection of
calix[4]resorcinarene derivs. with pendant acetal groups for chemical
amplified photoresist applications)

IT Positive photoresists

(chemical amplified; synthesis and photoinduced deprotection of calix[4]resorcinarene derivs. with pendant acetal groups for chemical amplified photoresist applications)

IT Acetyl group

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Photolysis
        (photoinduced deprotection of calix[4]resorcinarene derivs. with
        pendant acetal groups for chemical amplified photoresist
        applications)
ΙT
     Films
        (solubility and film-forming properties of calix[4]resorcinarene and its
        derivs. in relation to development of photoresists)
     Thermal stability
ΙT
        (synthesis and photoinduced deprotection of calix[4]resorcinarene
        derivs. with pendant acetal groups for chemical amplified
        photoresist applications)
     171799-35-2P 830329-32-3P
ΙT
     RL: PRP (Properties); RCT (Reactant); SPN (Synthetic preparation)
     ; PREP (Preparation); RACT (Reactant or reagent)
        (hydrolysis in aqueous KOH solution)
ΙT
     74227-35-3, Bis[4-(diphenylsulfonio)phenyl]sulfide bis[hexafluorophosphate
     RL: PRP (Properties)
        (photoacid generator; photoinduced deprotection of
        calix[4]resorcinarene derivs. with pendant acetal groups for chemical
        amplified photoresist applications)
     623159-10-4 623159-12-6
ΙT
     RL: RCT (Reactant); RACT (Reactant or reagent)
        (photoinduced deprotection of calix[4]resorcinarene derivs. with
        pendant acetal groups for chemical amplified photoresist
        applications)
     65338-98-9 176897-13-5
ΙT
     RL: PRP (Properties); RCT (Reactant); RACT (Reactant or reagent)
        (reaction with Et bromoacetate using K2CO3 in presence of TBAB as
       phase-transfer catalyst)
     64-17-5, Ethanol, uses 67-63-0, 2-Propanol, uses 67-64-1, Acetone,
            67-66-3, Chloroform, uses 67-68-5, DMSO, uses 68-12-2, DMF,
           75-59-2, Tetramethylammonium hydroxide 97-64-3, Ethyl lactate
     109-99-9, THF, uses 110-43-0, 2-Heptanone 110-54-3, Hexane, uses
     110-82-7, Cyclohexane, uses 123-91-1, Dioxane, uses 127-19-5, Dimethyl
                141-78-6, Ethyl acetate, uses 872-50-4, N-Methylpyrrolidone,
     acetamide
           7732-18-5, Water, uses 84540-57-8, Propylene glycol monomethyl
     uses
     ether acetate
     RL: NUU (Other use, unclassified); USES (Uses)
        (solubility and film-forming properties of calix[4]resorcinarene and its
        derivs. in relation to development of photoresists)
     130508-38-2P 710970-56-2P 830329-30-1P
     830329-31-2P
     RL: PRP (Properties); RCT (Reactant); SPN (Synthetic preparation)
     ; PREP (Preparation); RACT (Reactant or reagent)
        (synthesis and photoinduced deprotection of calix[4]resorcinarene
        derivs. with pendant acetal groups for chemical amplified
        photoresist applications)
REFERENCE COUNT:
                         20
                               THERE ARE 20 CITED REFERENCES AVAILABLE FOR THIS
                               RECORD. ALL CITATIONS AVAILABLE IN THE RE FORMAT
L22 ANSWER 5 OF 20 HCAPLUS COPYRIGHT 2009 ACS on STN
ACCESSION NUMBER:
                         2004:419455 HCAPLUS Full-text
DOCUMENT NUMBER:
                         142:143920
TITLE:
                        A chemically amplified calix[4]arene-based
                        electron-beam resist
AUTHOR(S):
                        Sailer, H.; Ruderisch, A.; Kern, D. P.; Schurig, V.
CORPORATE SOURCE:
                        Institute of Applied Physics, University of Tuebingen,
                        Tuebingen, 72076, Germany
SOURCE:
                        Microelectronic Engineering (2004), 73-74,
```

228-232

CODEN: MIENEF; ISSN: 0167-9317

PUBLISHER: Elsevier Science B.V.

DOCUMENT TYPE: Journal LANGUAGE: English

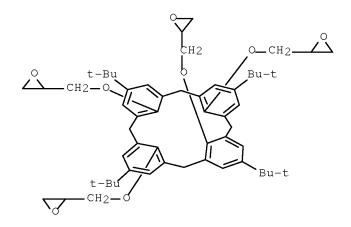
The concept of chemical amplification via cationic polymerization was applied to the novel class of calixarenes as nonpolymeric neg.-tone electron-beam resist materials for the first time. By using a calix[4] arene bearing epoxide residues and a photoacid generating triphenylsulfonium salt (PAG) as nonpolymeric chemical amplified resist system (npCAR) a tremendous increase of resist sensitivity was achieved. The high resolution capability of this npCAR is promising. Etching resistances of the npCAR and the commonly used novolak resins are comparable.

IT 140424-85-7P

RL: PRP (Properties); SPN (Synthetic preparation); TEM (Technical or engineered material use); PREP (Preparation); USES (Uses)

(neg. chemical amplified electron-beam resist containing calix[4]arene bearing epoxide residues and triphenylsulfonium salt)

RN 140424-85-7 HCAPLUS

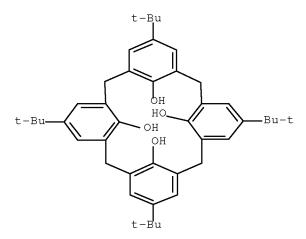


IT 60705-62-6

RL: RCT (Reactant); RACT (Reactant or reagent) (reaction with (±)-epichlorohydrin in presence of Cs2CO3)

RN 60705-62-6 HCAPLUS

CN Pentacyclo[19.3.1.13,7.19,13.115,19]octacosa-1(25),3,5,7(28),9,11,13(27),15,17,19(26),21,23-dodecaene-25,26,27,28tetrol, 5,11,17,23-tetrakis(1,1-dimethylethyl)- (CA INDEX NAME)



CC 74-5 (Radiation Chemistry, Photochemistry, and Photographic and Other Reprographic Processes)

ST calixarene based neg chem amplified electron beam lithog resist

IT Thickness

(neg. chemical amplified electron-beam resist containing calix[4] arene bearing epoxide residues and triphenylsulfonium salt)

IT Electron beam resists

(neg.-working, chemical amplified; neg. chemical amplified electron-beam resist containing calix[4]arene bearing epoxide residues and triphenylsulfonium salt)

IT 108-10-1, 4-Methylpentan-2-one

RL: NUU (Other use, unclassified); USES (Uses)

(developer; neg. chemical amplified electron-beam resist containing calix[4] arene bearing epoxide residues and triphenylsulfonium salt)

IT 140424-85-7P

RL: PRP (Properties); SPN (Synthetic preparation); TEM (Technical or engineered material use); FREP (Preparation); USES (Uses)

(neg. chemical amplified electron-beam resist containing

calix[4]arene bearing epoxide residues and triphenylsulfonium salt)

IT 60705-62-6

RL: RCT (Reactant); RACT (Reactant or reagent)

(reaction with (\pm) -epichlorohydrin in presence of Cs2CO3)

REFERENCE COUNT: 18 THERE ARE 18 CITED REFERENCES AVAILABLE FOR THIS RECORD. ALL CITATIONS AVAILABLE IN THE RE FORMAT

L22 ANSWER 6 OF 20 HCAPLUS COPYRIGHT 2009 ACS on STN ACCESSION NUMBER: 2004:326420 HCAPLUS <u>Full-text</u>

DOCUMENT NUMBER: 140:339079

TITLE: Preparation of chloromethylated calix[4] arene mixtures

for negative electron beam resists

INVENTOR(S): Momota, Junji; Oshima, Eiji

PATENT ASSIGNEE(S): Tokuyama Corp., Japan

SOURCE: Jpn. Kokai Tokkyo Koho, 11 pp.

CODEN: JKXXAF

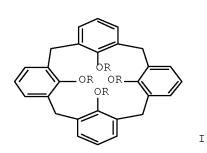
DOCUMENT TYPE: Patent LANGUAGE: Japanese

FAMILY ACC. NUM. COUNT: 1

PATENT INFORMATION:

PATENT NO. KIND DATE APPLICATION NO. DATE

____ _____ _____ JP 2004123586 Α 20040422 JP 2002-288430 20021001 <--JP 4118645 В2 20080716 PRIORITY APPLN. INFO.: JP 2002-288430 20021001 <--OTHER SOURCE(S): CASREACT 140:339079; MARPAT 140:339079



Calix[4]arenes I [R = (un)substituted C1-10 alkyl] are chloromethylated by HCl and HCHO in reaction systems containing 10-30 weight% H2O to give mixts. of tetrakis- and tris(chloromethylated) I. I (R = Me) (1.21 g) was treated with a mixture of 1,4-dioxane, AcOH, HCl, H3PO4, and 16 weight% H2O under reflux for 2 h to give 0.85 g 51:41 mixture of 5,11,17,23-tetrakis(chloromethyl)-I (R = Me) and 5,11,17-tris(chloromethyl)-I (R = Me).

IT 139934-98-8P 325814-49-1P 673458-26-9P 680223-95-4P

RL: IMF (Industrial manufacture); SPN (Synthetic preparation); PREP (Preparation)

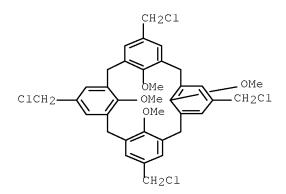
(preparation of chloromethylated calix[4]arene mixts. for neg. electron

beam

resists)

RN 139934-98-8 HCAPLUS

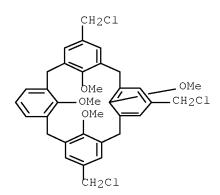
CN Pentacyclo[19.3.1.13,7.19,13.115,19]octacosa-1(25),3,5,7(28),9,11,13(27),15,17,19(26),21,23-dodecaene, 5,11,17,23-tetrakis(chloromethyl)-25,26,27,28-tetramethoxy- (CA INDEX NAME)



CN Pentacyclo[19.3.1.13,7.19,13.115,19]octacosa-1(25),3,5,7(28),9,11,13(27),15,17,19(26),21,23-dodecaene, 5,11,17,23-tetrakis(chloromethyl)-25,26,27,28-tetrapropoxy- (CA INDEX NAME)

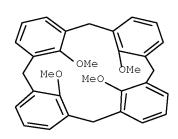
RN 673458-26-9 HCAPLUS

CN Pentacyclo[19.3.1.13,7.19,13.115,19]octacosa-1(25),3,5,7(28),9,11,13(27),15,17,19(26),21,23-dodecaene, 5,11,17-tris(chloromethyl)-25,26,27,28-tetramethoxy- (CA INDEX NAME)



RN 680223-95-4 HCAPLUS

CN Pentacyclo[19.3.1.13,7.19,13.115,19]octacosa-1(25),3,5,7(28),9,11,13(27),15,17,19(26),21,23-dodecaene, 5,11,17-tris(chloromethyl)-25,26,27,28-tetrapropoxy- (CA INDEX NAME)



147782-22-7 HCAPLUS RN CN Pentacyclo[19.3.1.13,7.19,13.115,19]octacosa-1(25),3,5,7(28),9,11,13(27),15,17,19(26),21,23-dodecaene, 25,26,27,28-tetrapropoxy- (CA INDEX NAME) *** STRUCTURE DIAGRAM IS NOT AVAILABLE *** ICM C07C041-22 IC ICS C07C043-225 CC 25-29 (Benzene, Its Derivatives, and Condensed Benzenoid Compounds) Section cross-reference(s): 74 calixarene chloromethylation water hydrochloric acid formaldehyde; neg ST electron beam resist calixarene chloromethylated ΙT Electron beam resists (neg.-working; preparation of chloromethylated calix[4]arene mixts. for neq. electron beam resists) Chloromethylation ΙT (preparation of chloromethylated calix[4] arene mixts. for neg. electron beam

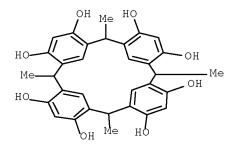
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resists)
ΙT
     7732-18-5, Water, uses
     RL: NUU (Other use, unclassified); USES (Uses)
        (concentration control; preparation of chloromethylated calix[4]arene
mixts. for
        neg. electron beam resists)
ΙT
     139934-98-8P 325814-49-1P 673458-26-9P
     680223-95-4P
     RL: IMF (Industrial manufacture); SPN (Synthetic
     preparation); PREP (Preparation)
        (preparation of chloromethylated calix[4] arene mixts. for neg. electron
beam
        resists)
     99095-68-8 147782-22-7,
ΙT
     25,26,27,28-Tetrapropoxycalix[4]arene
     RL: RCT (Reactant); RACT (Reactant or reagent)
        (preparation of chloromethylated calix[4] arene mixts. for neg. electron
beam
        resists)
L22 ANSWER 7 OF 20 HCAPLUS COPYRIGHT 2009 ACS on STN
ACCESSION NUMBER:
                         2004:140951 HCAPLUS Full-text
DOCUMENT NUMBER:
                         141:44772
                         A new positive-working alkaline developable
TITLE:
                         photoresist based on partially
                         O-tert-butoxycarbonylmethylated-tetra-C-
                         methylcalix[4]resorcinarene and a photoacid generator
                         Iimori, H.; Shibasaki, Y.; Ueda, M.; Ishii, H.
AUTHOR(S):
CORPORATE SOURCE:
                         Department of Organic and Polymeric Materials,
                         Graduate School of Science and Engineering, Tokyo
                         Institute of Technology, Tokyo, 152-8552, Japan
SOURCE:
                         Journal of Photopolymer Science and Technology (
                         2003), 16(5), 685-690
                         CODEN: JSTEEW; ISSN: 0914-9244
PUBLISHER:
                         Technical Association of Photopolymers, Japan
DOCUMENT TYPE:
                         Journal
LANGUAGE:
                         English
     A new pos.-working low-mol.-weight photoresist has been developed. The
AΒ
     photoresist consisted of the matrix, tetra-C-methylcalix[4]resorcinarene (p-t-
     BM-C4-R) in which the OH groups were protected with tert-butoxycarbonylmethyl
     groups (protecting ratio: 27-60%), and a photoacid generator (PAG), 5-
     (propylsulfonyloxyimino-5H-thiophen-2-ylidene)-2- methylphenylacetonitrile
     (PTMA). The p-t-BM-C4-R (protecting ratio: 40%) containing PTMA (2 wt%)
     showed a high sensitivity (10 mJ/cm2) and a contrast 11 after the irradiation
     with g-line, post-exposure baking at 120°C at 60 s, and developing with 2.38
     wt% tetramethylammonium hydroxide aqueous solution (TMAHaq) at 20°C for 10 s.
ΙT
     65338-98-9DP, tert-butoxycarbonylmethylated
     RL: PRP (Properties); SPN (Synthetic preparation); TEM
     (Technical or engineered material use); PREP (Preparation); USES
     (Uses)
        (pos.-working alkaline developable photoresist based on partially
        O-tert-butoxycarbonylmethylatedtetra-C-methylcalix[4]resorcinarene)
     65338-98-9 HCAPLUS
RN
     Pentacyclo[19.3.1.13,7.19,13.115,19]octacosa-
     1(25),3,5,7(28),9,11,13(27),15,17,19(26),21,23-dodecaene-
     4,6,10,12,16,18,22,24-octol, 2,8,14,20-tetramethyl- (CA INDEX NAME)
```

IT 65338-98-9

RL: RCT (Reactant); RACT (Reactant or reagent)
(preparation of partially O-tert-butoxycarbonylmethylatedtetra-C-methylcalix[4]resorcinarene)

RN 65338-98-9 HCAPLUS

CN Pentacyclo[19.3.1.13,7.19,13.115,19]octacosa-1(25),3,5,7(28),9,11,13(27),15,17,19(26),21,23-dodecaene-4,6,10,12,16,18,22,24-octol, 2,8,14,20-tetramethyl- (CA INDEX NAME)



CC 74-5 (Radiation Chemistry, Photochemistry, and Photographic and Other Reprographic Processes)

ST pos photoresist butoxycarbonylmethylated methylcalix resorcinarene

IT Photolithography

Positive photoresists

Solubility

ΙT

Thermal stability

(pos.-working alkaline developable photoxesist based on partially O-tert-butoxycarbonylmethylated tetra-C-methylcalix[4]resorcinarene)

IT 65338-98-9DP, tert-butoxycarbonylmethylated

RL: PRP (Properties); SPN (Synthetic preparation); TEM (Technical or engineered material use); PREP (Preparation); USES (Uses)

(pos.-working alkaline developable photoresist based on partially O-tert-butoxycarbonylmethylatedtetra-C-methylcalix[4]resorcinarene) 282713-83-1

RL: TEM (Technical or engineered material use); USES (Uses) (pos.-working alkaline developable photoresist based on partially

O-tert-butoxycarbonylmethylatedtetra-C-methylcalix[4]resorcinarene)

IT 5292-43-3, tert-Butyl bromoacetate **65338-98-9**

RL: RCT (Reactant); RACT (Reactant or reagent)

(preparation of partially O-tert-butoxycarbonylmethylatedtetra-C-

methylcalix[4]resorcinarene)

REFERENCE COUNT: 15 THERE ARE 15 CITED REFERENCES AVAILABLE FOR THIS RECORD. ALL CITATIONS AVAILABLE IN THE RE FORMAT

L22 ANSWER 8 OF 20 HCAPLUS COPYRIGHT 2009 ACS on STN ACCESSION NUMBER: 2004:57508 HCAPLUS $\underline{\text{Full-text}}$

DOCUMENT NUMBER: 140:112493

TITLE: Calix resorcinarene derivatives soluble in various

solvents and their heat-resistant flat films free from

crystallization

INVENTOR(S): Momota, Junji; Onishi, Hironori

PATENT ASSIGNEE(S): Tokuyama Corp., Japan

SOURCE: Jpn. Kokai Tokkyo Koho, 30 pp.

CODEN: JKXXAF

DOCUMENT TYPE: Patent LANGUAGE: Japanese

FAMILY ACC. NUM. COUNT: 1

PATENT INFORMATION:

PATENT NO.	KIND	DATE	APPLICATION NO.	DATE
JP 2004018421	A	20040122	JP 2002-173350	20020613 <
PRIORITY APPLN. INFO.:			JP 2002-173350	20020613 <
OTHER SOURCE(S):	MARPAT	140:112493		

GΙ

Calix resorcinarene derivs., useful for neg. electron beam resist materials, are represented by general formula I [R1-R3 = H, group shown as (a) C1-20 alkyl, amino, OH, aryl, aryloxy, etc., (b) C6-20 aryl, halo, amino, OH, aryl, aryloxy, etc., (c) C2-20 saturated aliphatic acyl, aromatic acyl, (d) YZ (Y = bond, divalent organic group; Z = ethenyl, halogenoalkyl); R2 \neq R3 \neq H; R4 = C1-20 (un)substituted alkyl halo; k = 0, 1, 2]. Thus, 0.6 mol resorcinol was reacted with 0.2 mol paraformaldehyde to yield 5 g of a white solid of an intermediate, then it (3.67 mmol) was esterified with 33 mmol methacryloyl chloride to yield 2.7 g of a white solid of I [R1 = Me, R2 = R3 = C(0)CMe:CH2; k = 0 (II)] showing good solubility in various solvents. Propylene glycol monomethyl ether solution of II gave a flat film free from crystals by spin coating on glass plate followed by drying. A mixture comprising II 50, tetraethylene glycol dimethacrylate 45, α -methylstyrene 5, α -methylstyrene dimer 1, and Perbutyl ND (tert-butylperoxy neodecanoate) was cast-polymerized

Т

while heating up from 30° to 90° to give 2-mm thick test pieces showing high hardness and thermal stability.

IT 646475-35-6P

RL: TMF (Industrial manufacture); PREP (Preparation)
 (solvent-soluble polymerizable calix resorcinarene derivs. for neg. EB
 resist materials and their heat-resistant crystal-free flat
 films)

RN 646475-35-6 HCAPLUS

CN 2-Propenoic acid, 2-methyl-, 2,8,14,20tetramethylpentacyclo[19.3.1.13,7.19,13.115,19]octacosa-1(25),3,5,7(28),9,11,13(27),15,17,19(26),21,23-dodecaene-4,6,10,12,16,18,22,24-octayl ester, homopolymer (9CI) (CA INDEX NAME)

CM 1

CRN 646474-80-8 CMF C64 H64 O16

IT 65338-98-9P 646475-05-0P

RL: IMF (Industrial manufacture); RCT (Reactant); PREP (Preparation); RACT (Reactant or reagent) (solvent-soluble polymerizable calix resorcinarene derivs. for neg. EB resist materials and their heat-resistant crystal-free flat films)

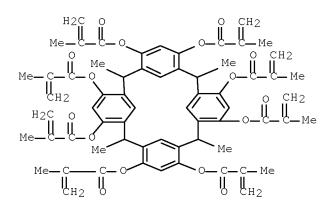
RN 65338-98-9 HCAPLUS

Pentacyclo[19.3.1.13,7.19,13.115,19]octacosa1(25),3,5,7(28),9,11,13(27),15,17,19(26),21,23-dodecaene4,6,10,12,16,18,22,24-octol, 2,8,14,20-tetramethyl- (CA INDEX NAME)

RN 646475-05-0 HCAPLUS CN Pentacyclo[19.3.1.13,7.19,13.115,19]octacosa-1(25),3,5,7(28),9,11,13(27),15,17,19(26),21,23-dodecaene-4,10,16,22tetrol, 6,12,18,24-tetramethoxy-2,8,14,20-tetramethyl- (CA INDEX NAME)

646474-80-8P 646474-81-9P 646474-83-1P ΙT 646474-87-5P 646474-89-7P 646474-91-1P 646474-94-4P 646474-98-8P 646475-02-7P 646475-08-3P 646475-11-8P 646475-14-1P 646475-16-3P 646475-18-5P 646475-20-9P 646475-22-1P 646475-24-3P 646475-26-5P 646475-29-8P 646475-31-2P 646475-33-4P RL: IMF (Industrial manufacture); TEM (Technical or engineered material use); PREP (Preparation); USES (Uses) (solvent-soluble polymerizable calix resorcinarene derivs. for neg. EB resist materials and their heat-resistant crystal-free flat films) 646474-80-8 HCAPLUS RN 2-Propenoic acid, 2-methyl-, 2,8,14,20-CN tetramethylpentacyclo[19.3.1.13,7.19,13.115,19]octacosa-1(25), 3, 5, 7(28), 9, 11, 13(27), 15, 17, 19(26), 21, 23-dodecaene-

4,6,10,12,16,18,22,24-octayl ester (9CI) (CA INDEX NAME)



RN 646474-81-9 HCAPLUS CN 2-Propenoic acid, 2,8,14,20tetramethylpentacyclo[19.3.1.13,7.19,13.115,19]octacosa-1(25),3,5,7(28),9,11,13(27),15,17,19(26),21,23-dodecaene-

4,6,10,12,16,18,22,24-octayl ester (9CI) (CA INDEX NAME)

RN 646474-83-1 HCAPLUS

CN Pentacyclo[19.3.1.13,7.19,13.115,19]octacosa-1(25),3,5,7(28),9,11,13(27),15,17,19(26),21,23-dodecaene, 4,6,10,12,16,18,22,24-octakis(chloromethoxy)-2,8,14,20-tetramethyl-INDEX NAME) (CA

RN 646474-87-5 HCAPLUS

CN Pentacyclo[19.3.1.13,7.19,13.115,19]octacosa-1(25),3,5,7(28),9,11,13(27),15,17,19(26),21,23-dodecaene, 2,8,14,20-tetrakis(chloromethyl)-4,10,16,22-tetramethoxy-6,12,18,24tetrakis(2-propen-1-yloxy)- (CA INDEX NAME)

RN 646474-89-7 HCAPLUS

CN Pentacyclo[19.3.1.13,7.19,13.115,19]octacosa-1(25),3,5,7(28),9,11,13(27),15,17,19(26),21,23-dodecaene, 4,6,10,12,16,18,22,24-octakis[[4-(chloromethyl)phenyl]methoxy]-2,8,14,20tetramethyl- (CA INDEX NAME)

PAGE 1-A

PAGE 2-A

PAGE 3-A

RN 646474-91-1 HCAPLUS

CN Pentacyclo[19.3.1.13,7.19,13.115,19]octacosa-1(25),3,5,7(28),9,11,13(27),15,17,19(26),21,23-dodecaene, 2,8,14,20-tetrakis(chloromethyl)-4,6,10,12,16,18,22,24-octamethoxy-INDEX NAME) (CA

RN 646474-94-4 HCAPLUS

CN 2-Propenoic acid, 2-methyl-, 6,12,18,24-tetramethoxy-2,8,14,20-tetraoctylpentacyclo[19.3.1.13,7.19,13.115,19]octacosa-1(25),3,5,7(28),9,11,13(27),15,17,19(26),21,23-dodecaene-4,10,16,22-tetrayl ester (9CI) (CA INDEX NAME)

RN 646474-98-8 HCAPLUS

CN Pentacyclo[19.3.1.13,7.19,13.115,19]octacosa-1(25),3,5,7(28),9,11,13(27),15,17,19(26),21,23-dodecaene, 5,11,17,23-tetrakis(chloromethyl)-4,6,10,12,16,18,22,24-octamethoxy-2,8,14,20-tetramethyl- (CA INDEX NAME)

RN 646475-02-7 HCAPLUS

CN Pentacyclo[19.3.1.13,7.19,13.115,19]octacosa-1(25),3,5,7(28),9,11,13(27),15,17,19(26),21,23-dodecaene, 5,11,17,23,25,26,27,28-octakis(chloromethyl)-4,6,10,12,16,18,22,24octamethoxy-2,8,14,20-tetramethyl- (CA INDEX NAME)

RN 646475-08-3 HCAPLUS

CN 2-Propenoic acid, 2-methyl-, [4,10,16,22-tetramethoxy-6,12,18,24-tetrakis[(2-methyl-1-oxo-2-propenyl)oxy]pentacyclo[19.3.1.13,7.19,13.115,19]octacosa-1(25),3,5,7(28),9,11,13(27),15,17,19(26),21,23-dodecaene-2,8,14,20-tetrayl]tetrakis(methylene-4,1-phenylene) ester (9CI) (CA INDEX NAME)

PAGE 2-A

RN 646475-11-8 HCAPLUS

CN Pentacyclo[19.3.1.13,7.19,13.115,19]octacosa-1(25),3,5,7(28),9,11,13(27),15,17,19(26),21,23-dodecaene, 5,11,17,23-tetrabromo-4,6,10,12,16,18,22,24-octakis(methoxymethoxy)-2,8,14,20-tetramethyl- (CA INDEX NAME)

RN 646475-14-1 HCAPLUS

CN Pentacyclo[19.3.1.13,7.19,13.115,19]octacosa-1(25),3,5,7(28),9,11,13(27),15,17,19(26),21,23-dodecaene, 4,6,10,12,16,18,22,24-octamethoxy-2,8,14,20-tetrakis[[4-(1-propen-1yl)phenyl]methyl]- (CA INDEX NAME)

RN 646475-16-3 HCAPLUS

CN 2-Propenoic acid, 2-methyl-, (2,8,14,20-tetramethylpentacyclo[19.3.1.13,7.19,13.115,19]octacosa-1(25),3,5,7(28),9,11,13(27),15,17,19(26),21,23-dodecaene-4,6,10,12,16,18,22,24-octayl)octa-2,1-ethanediyl ester (9CI) (CA INDEX NAME)

RN 646475-18-5 HCAPLUS

CN Pentacyclo[19.3.1.13,7.19,13.115,19]octacosa-1(25),3,5,7(28),9,11,13(27),15,17,19(26),21,23-dodecaene, 4,6,10,12,16,18,22,24-octakis(2-propen-1-yloxy)-2,8,14,20-tetrakis[[4-(2-propen-1-yloxy)phenyl]methyl]- (CA INDEX NAME)

PAGE 1-A

$$CH_2$$
 CH_2
 CH

PAGE 1-B

— СН<u>——</u> СН 2

PAGE 2-A

R2

$$CH_2-CH$$
 CH_2
 CH_2
 CH_2
 $R3$
 $R4$
 H_2C
 CH_2
 CH_2

RN 646475-20-9 HCAPLUS

CN 2-Propenoic acid, 2-methyl-, 2,8,14,20tetramethylpentacyclo[19.3.1.13,7.19,13.115,19]octacosa1(25),3,5,7(28),9,11,13(27),15,17,19(26),21,23-dodecaene4,6,10,12,16,18,22,24-octayl ester, polymer with (1-methylethenyl)benzene
and oxybis(2,1-ethanediyloxy-2,1-ethanediyl) bis(2-methyl-2-propenoate)
(9CI) (CA INDEX NAME)

CM 1

CRN 646474-80-8 CMF C64 H64 O16

CM 2

CRN 109-17-1 CMF C16 H26 O7

PAGE 1-B

CM 3

CRN 98-83-9 CMF C9 H10

RN 646475-22-1 HCAPLUS

CN 2-Propenoic acid, 2-methyl-, oxybis(2,1-ethanediyloxy-2,1-ethanediyl) ester, polymer with (1-methylethenyl)benzene and 2,8,14,20-tetramethylpentacyclo[19.3.1.13,7.19,13.115,19]octacosa-1(25),3,5,7(28),9,11,13(27),15,17,19(26),21,23-dodecaene-4,6,10,12,16,18,22,24-octayl octa-2-propenoate (9CI) (CA INDEX NAME)

CM 1

CRN 646474-81-9 CMF C56 H48 O16

CM 2

CRN 109-17-1 CMF C16 H26 O7

PAGE 1-B

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CM 3

CRN 98-83-9 CMF C9 H10

RN 646475-24-3 HCAPLUS

CN 2-Propenoic acid, 2-methyl-, oxybis(2,1-ethanediyloxy-2,1-ethanediyl) ester, polymer with (1-methylethenyl)benzene and 2,8,14,20-tetrakis(chloromethyl)-4,10,16,22-tetramethoxy-6,12,18,24-tetrakis(2-propenyloxy)pentacyclo[19.3.1.13,7.19,13.115,19]octacosa-1(25),3,5,7(28),9,11,13(27),15,17,19(26),21,23-dodecaene (9CI) (CA INDEX NAME)

CM 1

CRN 646474-87-5 CMF C48 H52 C14 O8

$$\begin{array}{c} \text{H}_2\text{C} = \text{CH} - \text{CH}_2 - \text{O} \\ \text{C1CH}_2 \\ \text{MeO} \\ \text{O} = \text{CH}_2 - \text{CH} = \text{CH}_2 \\ \text{OMe} \\ \text{C1CH}_2 \\ \text{MeO} \\ \text{O} = \text{CH}_2 - \text{CH} = \text{CH}_2 \\ \text{O} = \text{CH}_2 - \text{CH}_2 \\ \text{CH}_2 - \text{CH}_2 - \text{CH}_2 \\ \text{O} = \text{CH}_2 - \text{CH}_2 \\ \text{CH}_2 - \text{CH}_2 - \text{CH}_2 \\ \text{CH}_2 - \text{CH}_2 \\ \text{CH}_2 - \text{CH}_2 \\ \text{CH}_2 - \text{CH}_2 - \text{CH}_2 \\ \text{CH}_2 - \text{CH}_2 \\ \text{CH}_2 - \text{CH}_2 \\ \text{CH}_2 - \text{CH}_2 - \text{CH}_2 \\ \text{CH}_2 \\ \text{CH}_2 - \text{CH}_2 \\ \text{CH}_2 - \text{CH}_2 \\ \text$$

CM 2

CRN 109-17-1 CMF C16 H26 O7

PAGE 1-B

<u>—</u>Ме

CM 3

CRN 98-83-9

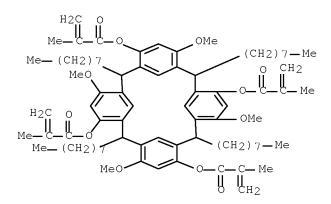
CMF C9 H10

RN 646475-26-5 HCAPLUS

CN 2-Propenoic acid, 2-methyl-, 6,12,18,24-tetramethoxy-2,8,14,20-tetraoctylpentacyclo[19.3.1.13,7.19,13.115,19]octacosa-1(25),3,5,7(28),9,11,13(27),15,17,19(26),21,23-dodecaene-4,10,16,22-tetrayl ester, polymer with (1-methylethenyl)benzene and oxybis(2,1-ethanediyloxy-2,1-ethanediyl) bis(2-methyl-2-propenoate) (9CI) (CA INDEX NAME)

CM 1

CRN 646474-94-4 CMF C80 H112 O12



CM 2

CRN 109-17-1 CMF C16 H26 O7

PAGE 1-B

CM 3

CRN 98-83-9 CMF C9 H10

RN 646475-29-8 HCAPLUS

CN 2-Propenoic acid, 2-methyl-, [4,10,16,22-tetramethoxy-6,12,18,24-tetrakis[(2-methyl-1-oxo-2-propenyl)oxy]pentacyclo[19.3.1.13,7.19,13.115,19]octacosa-1(25),3,5,7(28),9,11,13(27),15,17,19(26),21,23-dodecaene-2,8,14,20-tetrayl]tetrakis(methylene-4,1-phenylene) ester, polymer with (1-methylethenyl)benzene and oxybis(2,1-ethanediyloxy-2,1-ethanediyl)bis(2-methyl-2-propenoate) (9CI) (CA INDEX NAME)

CM 1

CRN 646475-08-3 CMF C92 H88 O20

PAGE 2-A

$$Me = \begin{bmatrix} 0 & & & \\ & & & \\ & & & \\ & & & \\ & & & \\ & & & \\ & & & \\ & & & \\ & & & \\ & & & \\ & & & \\ & & & \\ & & & \\ & & & \\ & & & \\ & & & \\ & & & \\ & & & \\ & & & \\ & & & \\ & & & \\ & & & \\ & & & \\ & & & \\ & & & \\ & & & \\ & & & \\ & & & \\ & & & \\ & & & \\ & & & \\ & & & \\ & & & \\ & & & \\ & & & \\ & & & \\ & & & \\ & & & \\ & & & \\ & & & \\ & & & \\ & & & \\ & & & \\ & & & \\ & & & \\ & & & \\ & & & \\ & & & \\ & & & \\ & & & \\ & & & \\ & & & \\ & & & \\ & & & \\ & & & \\ & & & \\ & & & \\ & & & \\ & & & \\ & & & \\ & & & \\ & & & \\ & & & \\ & & & \\ & & & \\ & & & \\ & & & \\ & & & \\ & & & \\ & & & \\ & & & \\ & & & \\ & & & \\ & & & \\ & & & \\ & & & \\ & & & \\ & & & \\ & & & \\ & & & \\ & & & \\ & & & \\ & & & \\ & & & \\ & & & \\ & & & \\ & & & \\ & & & \\ & & & \\ & & & \\ & & & \\ & & & \\ & & & \\ & & & \\ & & & \\ & & & \\ & & & \\ & & & \\ & & & \\ & & & \\ & & & \\ & & & \\ & & & \\ & & & \\ & & & \\ & & & \\ & & & \\ & & & \\ & & & \\ & & & \\ & & & \\ & & & \\ & & & \\ & & & \\ & & & \\ & & & \\ & & & \\ & & & \\ & & & \\ & & & \\ & & & \\ & & & \\ & & & \\ & & & \\ & & & \\ & & & \\ & & & \\ & & & \\ & & & \\ & & & \\ & & & \\ & & & \\ & & & \\ & & & \\ & & & \\ & & & \\ & & & \\ & & & \\ & & & \\ & & & \\ & & & \\ & & & \\ & & & \\ & & & \\ & & & \\ & & & \\ & & & \\ & & & \\ & & & \\ & & & \\ & & & \\ & & & \\ & & & \\ & & & \\ & & & \\ & & & \\ & & & \\ & & & \\ & & & \\ & & & \\ & & & \\ & & & \\ & & & \\ & & & \\ & & & \\ & & & \\ & & & \\ & & & \\ & & & \\ & & & \\ & & & \\ & & & \\ & & & \\ & & & \\ & & & \\ & & & \\ & & & \\ & & & \\ & & & \\ & & & \\ & & & \\ & & & \\ & & & \\ & & & \\ & & & \\ & & & \\ & & & \\ & & & \\ & & & \\ & & & \\ & & & \\ & & & \\ & & & \\ & & & \\ & & & \\ & & & \\ & & & \\ & & & \\ & & & \\ & & & \\ & & & \\ & & & \\ & & & \\ & & & \\ & & & \\ & & & \\ & & & \\ & & & \\ & & & \\ & & & \\ & & & \\ & & & \\ & & & \\ & & & \\ & & & \\ & & & \\ & & & \\ & & & \\ & & & \\ & & & \\ & & & \\ & & & \\ & & & \\ & & & \\ & & & \\ & & & \\ & & & \\ & & & \\ & & & \\ & & & \\ & & & \\ & & & \\ & & & \\ & & & \\ & & & \\ & & & \\ & & & \\ & & & \\ & & & \\ & & & \\ & & & \\ & & & \\ & & & \\ & & & \\ & & & \\ & & & \\ & & & \\ & & & \\ & & & \\ & & & \\ & & & \\ & & & \\ & & & \\ & & & \\ & &$$

CM 2

CRN 109-17-1 CMF C16 H26 O7

PAGE 1-B

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CM 3

CRN 98-83-9 CMF C9 H10

RN 646475-31-2 HCAPLUS

CN 2-Propenoic acid, 2-methyl-, (2,8,14,20-tetramethylpentacyclo[19.3.1.13,7.19,13.115,19]octacosa-1(25),3,5,7(28),9,11,13(27),15,17,19(26),21,23-dodecaene-4,6,10,12,16,18,22,24-octayl)octakis(oxy-2,1-ethanediyl) ester, polymer with (1-methylethenyl)benzene and oxybis(2,1-ethanediyloxy-2,1-ethanediyl) bis(2-methyl-2-propenoate) (9CI) (CA INDEX NAME)

CM 1

CRN 646475-16-3 CMF C80 H96 O24

CM 2

CRN 109-17-1 CMF C16 H26 O7

PAGE 1-B

<u>—</u>Ме

CM 3

CRN 98-83-9 CMF C9 H10

RN 646475-33-4 HCAPLUS

CN 2-Propenoic acid, 2-methyl-, oxybis(2,1-ethanediyloxy-2,1-ethanediyl) ester, polymer with (1-methylethenyl)benzene and 4,6,10,12,16,18,22,24-octakis(2-propenyloxy)-2,8,14,20-tetrakis[[4-(2-propenyloxy)phenyl]methyl]pentacyclo[[19.3.1.13,7.19,13.115,19]octacosa-1(25),3,5,7(28),9,11,13(27),15,17,19(26),21,23-dodecaene (9CI) (CA INDEX NAME)

CM 1

CRN 646475-18-5 CMF C92 H96 O12

PAGE 1-A

$$H_2C$$
 $=$ CH_2 $CH_$

PAGE 1-B

— СН<u>—</u> СН 2

PAGE 2-A

$$CH_2$$
— CH — CH_2
 CH_2 — CH_2 — CH_2 — R_3
 R_4
 H_2C — CH — CH_2

CM 2

CRN 109-17-1

CMF C16 H26 O7

 $\begin{array}{c} \text{PAGE 1-A} \\ \text{H2C} \\ \text{Me} \\ \begin{array}{c} \text{C} \\ \end{array} \\ \text{C} \\ \text{O} \\ \text{CH2} \\ \text{CH2}$

PAGE 1-B

— Ме

CM 3

CRN 98-83-9 CMF C9 H10

CC 38-3 (Plastics Fabrication and Uses) Section cross-reference(s): 37, 74

ST polymerizable group contg calix resorcinarene film; heat resistance calix resorcinarene film; neg electron beam resist calix resorcinarene

IT Metacyclophanes

RL: IMF (Industrial manufacture); TEM (Technical or engineered material use); PREP (Preparation); USES (Uses)

(calixarenes; solvent-soluble polymerizable calix resorcinarene derivs. for neg. EB resist materials and their heat-resistant crystal-free flat films)

IT Electron beam resists

(neg.-working; solvent-soluble polymerizable calix resorcinarene derivs.
for neg. EB resist materials and their heat-resistant
crystal-free flat films)

IT Plastic films

(solvent-soluble polymerizable calix resorcinarene derivs. for neg. EB resist materials and their heat-resistant crystal-free flat films)

IT 646475~35~6P

RL: IMF (Industrial manufacture); PREP (Preparation) (solvent-soluble polymerizable calix resorcinarene derivs. for neg. EB

resist materials and their heat-resistant crystal-free flat
films)

IT 65338-98-9P 646475-05-0P

RL: IMF (Industrial manufacture); RCT (Reactant); PREP

(Preparation); RACT (Reactant or reagent)

(solvent-soluble polymerizable calix resorcinarene derivs. for neg. EB resist materials and their heat-resistant crystal-free flat films)

IT 646474-80-8P 646474-81-9P 646474-83-1P

646474-87-5P 646474-89-7P 646474-91-1P

646474-94-4P 646474-98-8P 646475-02-7P

646475-08-3P 646475-11-8P 646475-14-1P

646475-16-3P 646475-18-5P 646475-20-9P

646475-22-1P 646475-24-3P 646475-26-5P

646475-29-8P 646475-31-2P 646475-33-4P

RL: IMF (Industrial manufacture); TEM (Technical or engineered

material use); PREP (Preparation); USES (Uses)

(solvent-soluble polymerizable calix resorcinarene derivs. for neg. EB resist materials and their heat-resistant crystal-free flat films)

IT 50-00-0, Formaldehyde, reactions 107-20-0 108-46-3, Resorcinol, reactions 124-19-6, Nonanal 150-19-6 6751-75-3 7339-87-9 646474-96-6 646475-00-5 646475-12-9

RL: RCT (Reactant); RACT (Reactant or reagent)

(solvent-soluble polymerizable calix resorcinarene derivs. for neg. EB resist materials and their heat-resistant crystal-free flat films)

L22 ANSWER 9 OF 20 HCAPLUS COPYRIGHT 2009 ACS on STN ACCESSION NUMBER: 2003:527539 HCAPLUS $\underline{\text{Full-text}}$

DOCUMENT NUMBER: 139:85127

TITLE: Preparation of solvent-soluble calixarenes and their

smooth films

INVENTOR(S): Oshima, Eiji; Takenaka, Junji

PATENT ASSIGNEE(S): Tokuyama Corp., Japan

SOURCE: Jpn. Kokai Tokkyo Koho, 11 pp.

CODEN: JKXXAF

DOCUMENT TYPE: Patent LANGUAGE: Japanese

FAMILY ACC. NUM. COUNT: 1

PATENT INFORMATION:

PATENT NO.	KIND	DATE	APPLICATION NO.	DATE
JP 2003192649	А	20030709	JP 2001-397522	20011227 <
PRIORITY APPLN. INFO.:			JP 2001-397522	20011227 <
OTHER SOURCE(S):	MARPAT	139:85127		
GI				

AB Title compds. I [n = 4-10; R1 = (cyclo)alkyl, alkenyl, (meth)acryloyl, etc.; X = NR2R3; R2, R3 = H, (un)substituted alkyl, alkenyl, aryl; R2 = R3 \neq H; R2R3 may be linked to form ring], useful for electron beam resists (no data), are prepared by amination of I (n, R1 = same as above; X = C1). Thus, I (n = 6, R1 = Me, X = C1) was aminated by Et2NH at 50° for 3 h in CHC13 to give 74% I (n, R1 = same as above; X = NEt2), which showed high solubility in various organic solvents and no crystallization when formed into a film.

IT 139934--98--8

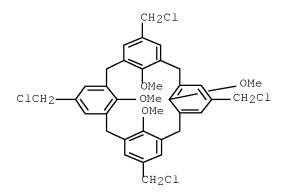
RL: RCT (Reactant); RACT (Reactant or reagent)
(preparation of solvent-soluble calixarenes and their crystal-free films

for

electron beam resists)

RN 139934-98-8 HCAPLUS

CN Pentacyclo[19.3.1.13,7.19,13.115,19]octacosa-1(25),3,5,7(28),9,11,13(27),15,17,19(26),21,23-dodecaene, 5,11,17,23-tetrakis(chloromethyl)-25,26,27,28-tetramethoxy- (CA INDEX NAME)



IT 556066-31-0P

RL: SPN (Synthetic preparation); TEM (Technical or engineered material use); PREP (Preparation); USES (Uses)

(preparation of solvent-soluble calixarenes and their crystal-free films

for

electron beam resists)

RN 556066-31-0 HCAPLUS

CN Pentacyclo[19.3.1.13,7.19,13.115,19]octacosa-1(25),3,5,7(28),9,11,13(27),15,17,19(26),21,23-dodecaene-5,11,17,23tetramethanamine, N5,N5,N11,N11,N17,N17,N23,N23-octaethyl-25,26,27,28tetramethoxy- (CA INDEX NAME)

```
ICM C07C217-58
TC
     ICS C07C213-02; C07C219-28; C07D295-08; G03F007-038
     25-29 (Benzene, Its Derivatives, and Condensed Benzenoid Compounds)
CC
     Section cross-reference(s): 74
ST
     calixarene prepn film electron beam resist; amination
     chloromethylcalixarene electron beam resist film
ΙT
    Metacyclophanes
     RL: SPN (Synthetic preparation); TEM (Technical or engineered material
     use); PREP (Preparation); USES (Uses)
        (calixarenes; preparation of solvent-soluble calixarenes and their crystal-
free
        films for electron beam resists)
     Electron beam resists
TT
        (neq.-working; preparation of solvent-soluble calixarenes and their
        crystal-free films for electron beam resists)
TΤ
     Films
        (preparation of solvent-soluble calixarenes and their crystal-free films
for
        electron beam resists)
TT
     Amines, reactions
     RL: RCT (Reactant); RACT (Reactant or reagent)
        (preparation of solvent-soluble calixarenes and their crystal-free films
for
        electron beam resists)
     109-73-9, Butylamine, reactions
                                       109-83-1, (2-Hydroxyethyl) methylamine
ΤТ
     109-89-7, Diethylamine, reactions 110-89-4, Piperidine, reactions
     111-42-2, Diethanolamine, reactions
                                          122-39-4, Diphenylamine, reactions
     124-02-7, Diallylamine
                            142-84-7, Dipropylamine
                                                       39216-86-9
                   124006-39-9 139934-98-8
     124006-38-8
                                             476687-13-5
                   556066-52-5
     556066-51-4
                                 556066-53-6
                                               556066-54-7
                                                             556066-55-8
     556066-56-9
     RL: RCT (Reactant); RACT (Reactant or reagent)
        (preparation of solvent-soluble calixarenes and their crystal-free films
for
        electron beam resists)
     556066-45-6P
                    556066-46-7P
                                   556066-47-8P
TT
     RL: RCT (Reactant); SPN (Synthetic preparation); TEM (Technical or
     engineered material use); PREP (Preparation); RACT (Reactant or reagent);
     USES (Uses)
        (preparation of solvent-soluble calixarenes and their crystal-free films
for
```

electron beam resists)

ΙT 556066-30-9P **556066-31-0P** 556066-32-1P 556066-33-2P

556066-34-3P 556066-35-4P 556066-36-5P 556066-37-6P 556066-38-7P 556066-39-8P 556066-40-1P 556066-41-2P 556066-42-3P 556066-43-4P

556066-44-5P 556066-48-9P 556066-49-0P 556066-50-3P

RL: SPN (Synthetic preparation); TEM (Technical or engineered material use); PREP (Preparation); USES (Uses)

(preparation of solvent-soluble calixarenes and their crystal-free films

for

electron beam resists)

L22 ANSWER 10 OF 20 HCAPLUS COPYRIGHT 2009 ACS on STN 2002:867239 HCAPLUS Full-text ACCESSION NUMBER:

DOCUMENT NUMBER: 137:377437

TITLE: Positive working radiation polymerizable compositions INVENTOR(S): Ueda, Mitsuru; Shibazaki, Yuji; Fujigaya, Takehiko;

Kwon, Yong Gil

PATENT ASSIGNEE(S): Jsr Ltd., Japan

Jpn. Kokai Tokkyo Koho, 8 pp. SOURCE:

CODEN: JKXXAF

DOCUMENT TYPE: Patent LANGUAGE: Japanese

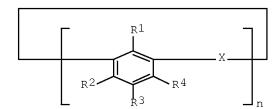
FAMILY ACC. NUM. COUNT:

PATENT INFORMATION:

PATENT NO.	KIND	DATE	APPLICATION NO.	DATE
JP 2002328473	A	20021115	JP 2001-134962	20010502 <
PRIORITY APPLN. INFO.:			JP 2001-134962	20010502 <
OTHER SOURCE(S):	MARPAT	137:377437		

OTHER SOURCE(S):

GΙ



Ι

AΒ The compns. comprise (A) cyclic polyphenolic compds. I (R1-4 = H, OH, halo,alkyl, aryl, aralkyl, alkoxy, alkenyl, acyl, alkoxycarbonyl, alkyloyloxy, aryloyloxy, cyano, nitro; ≥1 of R1-4 is tert-butoxycarbonyloxy; X = direct bond, CR5R6; R5-6 = H, alkyl, aryl; n = integer of 3-8) and (B) radiationsensitive acid generators. The compns. have high resolution and high sensitivity.

65338-98-9DP, tert-butoxycarbonyl derivs. 65338-98-9P ΤT RL: IMF (Industrial manufacture); RCT (Reactant); PREP (Preparation); RACT (Reactant or reagent) (calixarene-acid generator compns. for pos.-working

photoresists)

RN 65338-98-9 HCAPLUS

CN Pentacyclo[19.3.1.13,7.19,13.115,19]octacosa-1(25),3,5,7(28),9,11,13(27),15,17,19(26),21,23-dodecaene-4,6,10,12,16,18,22,24-octol, 2,8,14,20-tetramethyl- (CA INDEX NAME)

RN 65338-98-9 HCAPLUS

CN Pentacyclo[19.3.1.13,7.19,13.115,19]octacosa-1(25),3,5,7(28),9,11,13(27),15,17,19(26),21,23-dodecaene-4,6,10,12,16,18,22,24-octol, 2,8,14,20-tetramethyl- (CA INDEX NAME)

IT 250715-31-2P

RL: IMF (Industrial manufacture); TEM (Technical or engineered material use); FREP (Preparation); USES (Uses)

(calixarene-acid generator compns. for pos.-working photoresists)

RN 250715-31-2 HCAPLUS

```
ICM G03F007-039
IC
     ICS G03F007-004; H01L021-027
CC
     74-5 (Radiation Chemistry, Photochemistry, and Photographic and Other
     Reprographic Processes)
     Section cross-reference(s): 38
ST
     methylcalixresorcinarene acid generator pos photoresist;
     calixarene acid generator compn pos photoresist
     Positive photoresists
ΤT
        (calixarene-acid generator compns. for pos.-working
        photoresists)
     65338-98-9DP, tert-butoxycarbonyl derivs. 65338-98-9P
TT
     RL: IMF (Industrial manufacture); RCT (Reactant); PREP
     (Preparation); RACT (Reactant or reagent)
        (calixarene-acid generator compns. for pos.-working
        photoresists)
ΤT
     250715-31-2P
     RL: IMF (Industrial manufacture); TEM (Technical or engineered
     material use); PREP (Preparation); USES (Uses)
        (calixarene-acid generator compns. for pos.-working
        photoresists)
     75-07-0, Acetaldehyde, reactions
                                       108-46-3, Resorcinol, reactions
TΤ
     24424-99-5, Di-tert-butyl dicarbonate
     RL: RCT (Reactant); RACT (Reactant or reagent)
        (calixarene-acid generator compns. for pos.-working
        photoresists)
     137308-86-2, Diphenyliodonium 9,10-dimethoxyanthracene-2-sulfonate
ΙT
     RL: TEM (Technical or engineered material use); USES (Uses)
        (radiation-sensitive acid generator; calixarene-acid generator compns.
        for pos.-working photoresists)
L22 ANSWER 11 OF 20 HCAPLUS COPYRIGHT 2009 ACS on STN
ACCESSION NUMBER:
                         1999:513131 HCAPLUS Full-text
```

DOCUMENT NUMBER:

131:293195

Novel dissolution inhibitors based on calixarene derivatives for use in chemical amplification resists

AUTHOR(S):

Ito, Hiroshi; Nakayama, Tomonari; Ueda, Mitsuru; Sherwood, Mark; Miller, Dolores

CORPORATE SOURCE:

IBM Almaden Research Center, San Jose, CA, 95120, USA

SOURCE: Polymeric Materials Science and Engineering (

FOLYMETT Materials Science and Engineering (

1999), 81, 51-52

CODEN: PMSEDG; ISSN: 0743-0515

PUBLISHER: American Chemical Society

DOCUMENT TYPE: Journal LANGUAGE: English

AB Calix[4]resorcinarenes were synthesized by condensing resorcinol with aldehydes (acetaldehyde, benzaldehyde, and 4-isopropylbenzaldehyde) and separated into C4v and C2v, isomers. All eight OH groups were protected with acid-labile groups such as tBOC and tBuOCOCH2. The protected calixarenes have been found to be excellent dissoln. inhibitors for use in chemical amplification resists.

74410-61-0DP, t-butoxycarbonyl- or t-butoxycabonylmethyl-protected 145843-14-7DP, t-butoxycarbonyl- or t-butoxycabonylmethyl-protected 246023-01-8P 246023-03-0P 246023-04-1DP, t-butoxycarbonyl- or t-butoxycabonylmethyl-protected 246023-06-3P 246024-56-6DP, t-butoxycarbonyl- or t-butoxycabonylmethyl-protected RL: PRP (Properties); SPN (Synthetic preparation); TEM

(Technical or engineered material use); PREP (Preparation); USES (Uses)

(novel dissolm. inhibitors based on calix[4]resorcinarenes for use in chemical amplification resists)

RN 74410-61-0 HCAPLUS

CN Pentacyclo[19.3.1.13,7.19,13.115,19]octacosa-1(25),3,5,7(28),9,11,13(27),15,17,19(26),21,23-dodecaene-4,6,10,12,16,18,22,24-octol, 2,8,14,20-tetraphenyl-, stereoisomer (CA INDEX NAME)

Relative stereochemistry.

RN 145843-14-7 HCAPLUS CN Pentacyclo[19.3.1.13,7.19,13.115,19]octacosa-1(25),3,5,7(28),9,11,13(27),15,17,19(26),21,23-dodecaene-4,6,10,12,16,18,22,24-octol, 2,8,14,20-tetramethyl-,

 $(2\beta, 8\alpha, 14\beta, 20\alpha)$ – (CA INDEX NAME)

Relative stereochemistry.

RN 246023-04-1 HCAPLUS
CN Pentacyclo[19.3.1.13,7.19,13.115,19]octacosa1(25),3,5,7(28),9,11,13(27),15,17,19(26),21,23-dodecaene4,6,10,12,16,18,22,24-octol, 2,8,14,20-tetrakis[4-(1-methylethyl)phenyl]-,
stereoisomer (CA INDEX NAME)

Relative stereochemistry.

RN 246024-56-6 HCAPLUS
CN Pentacyclo[19.3.1.13,7.19,13.115,19]octacosa1(25),3,5,7(28),9,11,13(27),15,17,19(26),21,23-dodecaene4,6,10,12,16,18,22,24-octol, 2,8,14,20-tetraphenyl-,

4,6,10,12,16,18,22,24-octol, 2,8,14,20-tetraphenyl-, $(2\beta,8\alpha,14\beta,20\alpha)$ - (CA INDEX NAME)

Relative stereochemistry.

246023-05-2P 246024-56-6P

RL: RCT (Reactant); SPN (Synthetic preparation); PREP

(Preparation); RACT (Reactant or reagent)

(preparation of novel dissoln. inhibitors based on calix[4] resorcinarenes for use in chemical amplification resists)

RN 74410-61-0 HCAPLUS

CN Pentacyclo[19.3.1.13,7.19,13.115,19]octacosa-1(25),3,5,7(28),9,11,13(27),15,17,19(26),21,23-dodecaene-4,6,10,12,16,18,22,24-octol, 2,8,14,20-tetraphenyl-, stereoisomer (CA INDEX NAME)

Relative stereochemistry.

RN 74708-10-4 HCAPLUS

CN Pentacyclo[19.3.1.13,7.19,13.115,19]octacosa-1(25),3,5,7(28),9,11,13(27),15,17,19(26),21,23-dodecaene-4,6,10,12,16,18,22,24-octol, 2,8,14,20-tetramethyl-, stereoisomer (CA INDEX NAME)

Relative stereochemistry.

RN 145843-14-7 HCAPLUS

CN Pentacyclo[19.3.1.13,7.19,13.115,19]octacosa- 1(25),3,5,7(28),9,11,13(27),15,17,19(26),21,23-dodecaene- 4,6,10,12,16,18,22,24-octol, 2,8,14,20-tetramethyl-, $(2\beta,8\alpha,14\beta,20\alpha)$ - (CA INDEX NAME)

Relative stereochemistry.

RN 246023-04-1 HCAPLUS

CN Pentacyclo[19.3.1.13,7.19,13.115,19]octacosa-1(25),3,5,7(28),9,11,13(27),15,17,19(26),21,23-dodecaene-4,6,10,12,16,18,22,24-octol, 2,8,14,20-tetrakis[4-(1-methylethyl)phenyl]-, stereoisomer (CA INDEX NAME)

Relative stereochemistry.

RN 246023-05-2 HCAPLUS

CN Pentacyclo[19.3.1.13,7.19,13.115,19]octacosa- 1(25),3,5,7(28),9,11,13(27),15,17,19(26),21,23-dodecaene- 4,6,10,12,16,18,22,24-octol, 2,8,14,20-tetrakis[4-(1-methylethyl)phenyl]-, $(2\alpha,8\beta,14\alpha,20\beta)$ - (CA INDEX NAME)

RN 246024-56-6 HCAPLUS

CN Pentacyclo[19.3.1.13,7.19,13.115,19]octacosa- 1(25),3,5,7(28),9,11,13(27),15,17,19(26),21,23-dodecaene- 4,6,10,12,16,18,22,24-octol, 2,8,14,20-tetraphenyl-, $(2\beta,8\alpha,14\beta,20\alpha)$ - (CA INDEX NAME)

Relative stereochemistry.

CC 74-5 (Radiation Chemistry, Photochemistry, and Photographic and Other Reprographic Processes)

Section cross-reference(s): 38, 76

ST dissoln inhibitor calixarene chem amplification photoresist

IT Photolithography

Photoresists

Semiconductor device fabrication

(novel dissolm. inhibitors based on calix[4]resorcinarenes for use in chemical amplification resists)

IT Dendritic polymers

RL: PRP (Properties); SPN (Synthetic preparation); TEM (Technical or engineered material use); PREP (Preparation); USES (Uses)

(novel dissolm. inhibitors based on calix[4]resorcinarenes for use in chemical amplification resists)

IT 159296-87-4, 4-Hydroxystyrene-tert-butyl acrylate copolymer
RL: PEP (Physical, engineering or chemical process); TEM (Technical or engineered material use); PROC (Process); USES (Uses)

(novel dissoln. inhibitors based on calix[4]resorcinarenes for use in

```
chemical amplification resists)
ΤТ
     74410-61-0DP, t-butoxycarbonyl- or t-butoxycabonylmethyl-protected
     145843-14-7DP, t-butoxycarbonyl- or
     t-butoxycabonylmethyl-protected 246023-01-82
     246023-03-0P 246023-04-1DP, t-butoxycarbonyl- or
     t-butoxycabonylmethyl-protected 246023-06-3P
     246024-56-6DP, t-butoxycarbonyl- or
     t-butoxycabonylmethyl-protected
     RL: PRP (Properties); SPN (Synthetic preparation); TEM
     (Technical or engineered material use); PREP (Preparation); USES
     (Uses)
        (novel dissoln. inhibitors based on calix[4]resorcinarenes for use in
        chemical amplification resists)
     75-07-0, Acetaldehyde, reactions 100-52-7, Benzaldehyde, reactions
ΙT
     108-46-3, Resorcinol, reactions 122-03-2, 4-Isopropylbenzaldehyde
     5292-43-3, tert-Butyl bromoacetate 24424-99-5, Di-tert-butyl dicarbonate
     RL: RCT (Reactant); RACT (Reactant or reagent)
        (preparation of novel dissoln. inhibitors based on calix[4]resorcinarenes
        for use in chemical amplification resists)
     74410-61-0P 74708-10-4P 145843-14-7DP,
     t-butoxycarbonyl- or t-butoxycabonylmethyl-protected 246023-04-19
     246023-05-2P 246024-56-6P
     RL: RCT (Reactant); SPN (Synthetic preparation); PREP
     (Preparation); RACT (Reactant or reagent)
        (preparation of novel dissoln. inhibitors based on calix[4]resorcinarenes
        for use in chemical amplification resists)
REFERENCE COUNT:
                         16
                               THERE ARE 16 CITED REFERENCES AVAILABLE FOR THIS
                               RECORD. ALL CITATIONS AVAILABLE IN THE RE FORMAT
L22 ANSWER 12 OF 20 HCAPLUS COPYRIGHT 2009 ACS on STN
                         1999:44198 HCAPLUS Full-text
ACCESSION NUMBER:
DOCUMENT NUMBER:
                         130:202814
TITLE:
                         A New Photoresist Based on
                         Calix[4]resorcinarene Dendrimer
                         Haba, Osamu; Haga, Kohji; Ueda, Mitsuru; Morikawa,
AUTHOR(S):
                         Osamu; Konishi, Hisatoshi
CORPORATE SOURCE:
                         Department of Human Sensing and Functional Sensor
                         Engineering Graduate School of Engineering, Yamagata
                         University, Yamagata, 992-8510, Japan
SOURCE:
                         Chemistry of Materials (1999), 11(2),
                         427-432
                         CODEN: CMATEX; ISSN: 0897-4756
PUBLISHER:
                         American Chemical Society
DOCUMENT TYPE:
                         Journal
LANGUAGE:
                         English
AB
     A new dendrimer (1), which contains phenol groups in the exterior for
     solubilization in aqueous alkaline solution and calix[4]resorcinarene in the
     interior to increase the mol. weight and number of the phenol group even in
     the lower generation, was designed as new neg.-working, alkaline-developable
     photoresist material. A neg.-working photoresist based on 1, 2,6-
     bis(hydroxymethyl)phenol as crosslinker, and diphenyliodonium 9,10-
     dimethoxyanthracene-2-sulfonate as a photoacid generator was developed. This
     resist gave a clear neg. pattern through postbaking at 110° after exposure to
     UV light, followed by developing with a 0.3% aqueous Me4NOH solution at room
     temperature
     196298-31-4P
ΙT
     RL: RCT (Reactant); SPN (Synthetic preparation); PREP
     (Preparation); RACT (Reactant or reagent)
        (in synthesis of calix[4]resorcinarene dendrimer)
     196298-31-4 HCAPLUS
RN
```

CN Pentacyclo[19.3.1.13,7.19,13.115,19]octacosa-1(25),3,5,7(28),9,11,13(27),15,17,19(26),21,23-dodecaene, 4,6,10,12,16,18,22,24-octakis[[3,5-bis(2-propen-1-yloxy)phenyl]methoxy]-2,8,14,20-tetramethyl- (CA INDEX NAME)

PAGE 1-B

—CH=CH2

—— CH2—СН=— CH2

PAGE 2-A
$$\begin{array}{c} \text{R} \\ \text{O} \\ \text{CH}_2 \\ \text{H}_2\text{C} \underline{\hspace{0.5cm}} \text{CH}_2 \text{CH}_2 \text{CH}_2 \\ \text{CH}_2 \text{CH}_2 \text{CH}_2 \text{CH}_2 \end{array}$$

PAGE 3-A $\begin{array}{c}
R2\\
CH=CH2\\
H2C=CH-CH2-O-CH2
\end{array}$ $\begin{array}{c}
CH=CH2\\
O-CH2
\end{array}$ $\begin{array}{c}
CH=CH2\\
CH2
\end{array}$

PAGE 4-A
$$\begin{array}{c} \text{O-CH}_2\text{-CH-CH}_2 \\ \text{H}_2\text{C-CH-CH}_2 - \text{O} \\ \text{R}_4 \end{array}$$

PAGE 1-A

$$\begin{array}{c} \text{OH} \\ \text{HO} \\ \text{CH}_2 \\ \text{OH} \\ \text{R2} \\ \text{R} \\ \text{R3} \\ \end{array}$$

PAGE 2-A

PAGE 3-A

```
CC
     74-5 (Radiation Chemistry, Photochemistry, and Photographic and Other
     Reprographic Processes)
ST
     lithog photoresist calixresorcinarene dendrimer
IT
     Negative photoresists
        (lithog. characterization of new photoresist based on
        calix[4]resorcinarene dendrimer)
ΙT
     Dendritic polymers
     RL: TEM (Technical or engineered material use); USES (Uses)
        (lithog. characterization of new photoresist based on
        calix[4]resorcinarene dendrimer)
     2937-59-9, 2,6-Bis(hydroxymethyl)phenol
TΤ
     RL: TEM (Technical or engineered material use); USES (Uses)
        (crosslinker; lithog. characterization of new photoresist
        based on calix[4]resorcinarene dendrimer)
ΙT
     75-59-2, Tetramethylammonium hydroxide
     RL: NUU (Other use, unclassified); USES (Uses)
        (developer; lithog. characterization of new photoresist based
        on calix[4]resorcinarene dendrimer)
ΙT
     135710-38-2P, Methyl 3,5-di(allyloxy)benzoate
                                                     177837-80-8P,
     3,5-Di(allyloxy)benzyl alcohol 196298-31-4P
     RL: RCT (Reactant); SPN (Synthetic preparation); PREP
     (Preparation); RACT (Reactant or reagent)
        (in synthesis of calix[4]resorcinarene dendrimer)
     196298-30-3P
ΙT
     RL: PRP (Properties); SPN (Synthetic preparation); TEM
     (Technical or engineered material use); PREF (Preparation); USES
        (lithog, characterization of new photoresist based on
        calix[4]resorcinarene dendrimer)
     137308-86-2, Diphenyliodonium 9,10-dimethoxyanthracene-2-sulfonate
ΤТ
     RL: TEM (Technical or engineered material use); USES (Uses)
        (photoacid generator; lithog. characterization of new
        photoresist based on calix[4]resorcinarene dendrimer)
REFERENCE COUNT:
                               THERE ARE 14 CITED REFERENCES AVAILABLE FOR THIS
                         14
                               RECORD. ALL CITATIONS AVAILABLE IN THE RE FORMAT
L22 ANSWER 13 OF 20 HCAPLUS COPYRIGHT 2009 ACS on STN
                         1998:781642 HCAPLUS Full-text
ACCESSION NUMBER:
                         130:146122
DOCUMENT NUMBER:
TITLE:
                         A New Three-Component Photoresist Based on
                         Calix[4]resorcinarene Derivative, a Crosslinker, and a
                         Photoacid Generator
AUTHOR(S):
                         Nakayama, Tomonari; Nomura, Masayoshi; Haga, Kohji;
                         Ueda, Mitsuru
CORPORATE SOURCE:
                         Dep. Human Sensing and Functional Sensor Eng.,
                         Graduate School of Eng., Yamagata University,
                         Yonezawa, Yamagata, 992-8510, Japan
SOURCE:
                         Bulletin of the Chemical Society of Japan (
                         1998), 71(12), 2979-2984
                         CODEN: BCSJA8; ISSN: 0009-2673
                         Chemical Society of Japan
PUBLISHER:
DOCUMENT TYPE:
                         Journal
LANGUAGE:
                         English
     Calix[4]resorcinarene [2,8,14,20-tetramethylcalix[4]arene-
     4,6,10,12,16,18,22,24-octol; C4-RA](4) having p-hydroxybenzyl groups on its
     exterior was prepared by the condensation of C4-RA and p-(allyloxy)benzyl
     bromide, followed by the cleavage of allyl groups with palladium catalyst and
     ammonium formate. Compound 4 having high transparency to UV-light above 300
```

nm was considered for a new resist matrix. A three-component photoresist consisting of 4, 2,6-bis(hydroxymethyl)-4-methylphenol (BHMP), and diphenyliodonium 9,10-dimethoxyanthracene-2-sulfonate (DIAS) showed a sensitivity of 19 mJ cm-2(D1/2) and a contrast of 3.0 (γ 1/2) when it was exposed to 365 nm light and post-exposure baked (PEB) at 110 °C for 5 min, followed by developing with a 0.2 wt% aqueous tetramethylammonium hydroxide (TMAH) solution A fine neg. image featuring 1 μ m of min. line and space patterns was observed on film of the photoresist exposed to 40 mJ-cm-2of UV-light at 365 nm with a scanning electron microscope.

IT 220033-50-1P

RL: RCT (Reactant); SPN (Synthetic preparation); PREP (Preparation); RACT (Reactant or reagent)

(in synthesis of calix[4]resorcinarene derivative for photoresist formulation)

RN 220033-50-1 HCAPLUS

CN Pentacyclo[19.3.1.13,7.19,13.115,19]octacosa-1(25),3,5,7(28),9,11,13(27),15,17,19(26),21,23-dodecaene, 2,8,14,20-tetramethyl-4,6,10,12,16,18,22,24-octakis[[4-(2-propen-1-yloxy)phenyl]methoxy]- (CA INDEX NAME)

PAGE 1-B

—— CH2

— СН<u>—</u> СН 2

PAGE 2-A

PAGE 3-A

220033-49-82 ΙT

> RL: PRP (Properties); SPN (Synthetic preparation); TEM (Technical or engineered material use); PREP (Preparation); USES (Uses)

(lithog. characteristics of three-component photoresist consisting of calix[4]resorcinarene derivative matrix and crosslinker and photoacid generator)

220033-49-8 HCAPLUS RN

Phenol, 4,4',4'',4''',4'''',4'''',4''''',4''''',4''''' CN tetramethylpentacyclo[19.3.1.13,7.19,13.115,19]octacosa-1(25),3,5,7(28),9,11,13(27),15,17,19(26),21,23-dodecaene-4,6,10,12,16,18,22,24-octayl)octakis(oxymethylene)]octakis- (9CI) (CA INDEX NAME)

PAGE 1-A

PAGE 2-A

PAGE 3-A

- IT 74708-10-4
 - RL: RCT (Reactant); RACT (Reactant or reagent)

(reaction with allyloxybenzyl bromide and 18-crown-6 in synthesis of calix[4]resorcinarene derivative for photoresist formulation)

- RN 74708-10-4 HCAPLUS
- CN Pentacyclo[19.3.1.13,7.19,13.115,19]octacosa-1(25),3,5,7(28),9,11,13(27),15,17,19(26),21,23-dodecaene-

4,6,10,12,16,18,22,24-octol, 2,8,14,20-tetramethyl-, stereoisomer (CA INDEX NAME)

Relative stereochemistry.

- CC 74-5 (Radiation Chemistry, Photochemistry, and Photographic and Other Reprographic Processes)
- ST photoresist calixresorcinarene deriv crosslinker photoacid generator; lithog photoresist calixresorcinarene deriv
- IT Photoresists

(lithog. characteristics of three-component photoresist consisting of calix[4]resorcinarene derivative matrix and crosslinker and photoacid generator)

- IT Thermal properties
 - (of calix[4]resorcinarene derivative for photoresist formulation)
- IT 75-59-2, Tetramethylammonium hydroxide
 - RL: NUU (Other use, unclassified); USES (Uses)

(developer; lithog. characteristics of three-component

photoresist consisting of calix[4]resorcinarene derivative matrix
and crosslinker and photoacid generator)

IT 17455-13-9, 18-Crown-6

RL: RCT (Reactant); RACT (Reactant or reagent)

(in synthesis of calix[4]resorcinarene derivative for photoresist formulation)

IT 3256-45-9P, p-(Allyloxy)benzyl alcohol 143116-30-7P, p-(Allyloxy)benzyl bromide 220033-50-1P

RL: RCT (Reactant); SPN (Synthetic preparation); PREP

(Preparation); RACT (Reactant or reagent)

(in synthesis of calix[4]resorcinarene derivative for photoresist formulation)

IT 220033-49-8P

RL: PRP (Properties); SPN (Synthetic preparation); TEM (Technical or engineered material use); PREP (Preparation); USES (Uses)

(lithog. characteristics of three-component photoresist consisting of calix[4]resorcinarene derivative matrix and crosslinker and photoacid generator)

IT 91-04-3, 2,6-Bis(hydroxymethyl)-4-methylphenol 137308-86-2,
 Diphenyliodonium 9,10-dimethoxyanthracene-2-sulfonate
 RL: PRP (Properties); TEM (Technical or engineered material use); USES

(Uses)

(lithog. characteristics of three-component photoresist consisting of calix[4]resorcinarene derivative matrix and crosslinker and

photoacid generator)

TT 74708-10-4

RL: RCT (Reactant); RACT (Reactant or reagent)

(reaction with allyloxybenzyl bromide and 18-crown-6 in synthesis of

calix[4]resorcinarene derivative for photoresist formulation)

THERE ARE 20 CITED REFERENCES AVAILABLE FOR THIS REFERENCE COUNT: 20

RECORD. ALL CITATIONS AVAILABLE IN THE RE FORMAT

L22 ANSWER 14 OF 20 HCAPLUS COPYRIGHT 2009 ACS on STN ACCESSION NUMBER: 1998:758628 HCAPLUS Full-text

DOCUMENT NUMBER: 130:73852

Phenolic dendrimer and radiation-sensitive composition TITLE:

containing it for resist

INVENTOR(S): Ueda, Mitsuru

PATENT ASSIGNEE(S): JSR Co., Ltd., Japan

Jpn. Kokai Tokkyo Koho, 25 pp. SOURCE:

CODEN: JKXXAF

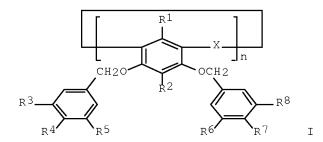
DOCUMENT TYPE: Patent LANGUAGE: Japanese

FAMILY ACC. NUM. COUNT:

PATENT INFORMATION:

<
<

GI



AΒ Title composition contains phenolic dendrimer I (R1-R8 = H, OH, halo, alkyl, aryl, aralkyl, alkoxy, alkenyl, alkenyloxy, acyl, alkoxycarbonyl, alkyloyloxy, aryloyloxy, cyano, NO2; ≥1 of R3-R8 = OH; X = single bond, CR9R10; R9, R10 = H, alkyl, aryl; n = 3-8). The composition is useful as resist showing high sensitivity and resolution

65338-98-9P 196298-31-4P ΤT

> RL: PNU (Preparation, unclassified); RCT (Reactant); PREP (Preparation); RACT (Reactant or reagent)

(in preparation of phenolic dendrimer for radiation-sensitive resist composition)

RN 65338-98-9 HCAPLUS

CN Pentacyclo[19.3.1.13,7.19,13.115,19]octacosa-1(25),3,5,7(28),9,11,13(27),15,17,19(26),21,23-dodecaene-4,6,10,12,16,18,22,24-octol, 2,8,14,20-tetramethyl- (CA INDEX NAME)

RN 196298-31-4 HCAPLUS

CN Pentacyclo[19.3.1.13,7.19,13.115,19]octacosa-1(25),3,5,7(28),9,11,13(27),15,17,19(26),21,23-dodecaene, 4,6,10,12,16,18,22,24-octakis[[3,5-bis(2-propen-1-yloxy)phenyl]methoxy]-2,8,14,20-tetramethyl- (CA INDEX NAME)

—СН<u>—</u>СН2

—— CH2— CH== CH2

PAGE 2-A
$$\begin{array}{c} \text{R} \\ \text{CH}_2 \\ \text{H}_2 \text{C} \underline{\hspace{0.5cm}} \text{CH}_2 - \text{CH}_2 - \text{CH}_2 \\ \end{array}$$

PAGE 4-A

IT 196298-30-3P

RL: PNU (Preparation, unclassified); TEM (Technical or engineered material use); PREP (Preparation); USES (Uses) (radiation-sensitive resist composition containing phenolic dendrimer) 196298-30-3 HCAPLUS

RN 196298-30-3 HCAPLUS
CN 1,3-Benzenediol, 5,5',5'',5''',5'''',5''''',5''''',5''''',5'''''-[(2,8,14,20-tetramethylpentacyclo[19.3.1.13,7.19,13.115,19]octacosa-1(25),3,5,7(28),9,11,13(27),15,17,19(26),21,23-dodecaene-4,6,10,12,16,18,22,24-octayl)octakis(oxymethylene)]octakis-(9CI) (CA INDEX NAME)

PAGE 2-A

PAGE 3-A

IC ICM C07C043-23

ICS G03F007-022; G03F007-038; H01L021-027

- CC 74-5 (Radiation Chemistry, Photochemistry, and Photographic and Other Reprographic Processes)
 Section cross-reference(s): 25
- ST phenolic dendrimer radiation sensitive resist
- IT Photoresists

 $(radiation-sensitive \ resist$ composition containing phenolic dendrimer)

IT Resists

(radiation-sensitive; radiation-sensitive resist composition containing phenolic dendrimer)

IT 13965-03-2P, Bis(triphenylphosphine)palladium(II) dichloride RL: CAT (Catalyst use); PNU (Preparation, unclassified); PREP (Preparation); USES (Uses)

(in preparation of phenolic dendrimer for radiation-sensitive ${\tt resist}$ composition)

- IT 2150-44-9P, Methyl 3,5-dihydroxybenzoate 65338-98-9P 135710-38-2P, Methyl 3,5-bis(allyloxy)benzoate 177837-80-8P 182058-69-1P 196298-31-4P
 - RL: PNU (Preparation, unclassified); RCT (Reactant); PREP (Preparation); RACT (Reactant or reagent)

(in preparation of phenolic dendrimer for radiation-sensitive xesist composition)

```
ΙT
     75-07-0, Acetaldehyde, reactions
                                        106-95-6, 3-Bromopropene, reactions
     108-46-3, Resorcinol, reactions
     RL: RCT (Reactant); RACT (Reactant or reagent)
        (in preparation of phenolic dendrimer for radiation-sensitive resist
        composition)
ΙT
     196298-30-3P
     RL: PNU (Preparation, unclassified); TEM (Technical or
     engineered material use); PREP (Preparation); USES (Uses)
        (radiation-sensitive resist composition containing phenolic dendrimer)
L22 ANSWER 15 OF 20 HCAPLUS COPYRIGHT 2009 ACS on STN
ACCESSION NUMBER:
                         1998:592926 HCAPLUS Full-text
DOCUMENT NUMBER:
                         129:283338
ORIGINAL REFERENCE NO.: 129:57637a,57640a
TITLE:
                         Calixarene and dendrimer as novel photoresist
                         materials
AUTHOR(S):
                         Haba, Osamu; Takahashi, Daisuke; Haga, Kohji; Sakai,
                         Yoshimasa; Nakayama, Tomonari; Ueda, Mitsuru
                         Department of Human Sensing and Functional Sensor
CORPORATE SOURCE:
                         Engineering, Graduate School of Engineering, Yamagata
                         University, Yamagata, 992, Japan
                         ACS Symposium Series (1998), 706 (Micro- and
SOURCE:
                         Nanopatterning Polymers), 237-248
                         CODEN: ACSMC8; ISSN: 0097-6156
                         American Chemical Society
PUBLISHER:
DOCUMENT TYPE:
                         Journal
                         English
LANGUAGE:
AB
     Neg.-working alkaline developable photoresists based on calix[4]-resorcinarene
     (1) or calixarene dendrimer (2), a crosslinker, and a photoacid generator have
     been developed. Compound 2 was prepared by the condensation of compound 1
     with 3,5-diallyloxybenzylbromide, followed by the removal of allyl groups.
     The resist consisting of 1 (70 wt%), a photoacid generator, diphenyliodonium
     9,10-dimethoxyanthracene-2-sulfonate (DIAS) (10 wt%), and 4,4-
     methylenebis[2,6-bis(hydroxymethyl)-phenol] (MBHP) (20 wt%) as a crosslinker
     showed a sensitivity of 2.2~\mathrm{mJ-cm-2} and a contrast of 3.1~\mathrm{when} it was exposed
     to 365 nm light and postbaked at 130°C for 3 min, followed by developing with
     a 0.1% aqueous tetramethylammonium hydroxide (TMAH) solution On the other
     hand, the resist formulated by mixing 2 (70 wt%), DIAS (10 wt%), and the
     crosslinker, 2,6-bis(hydroxymethyl)phenol (BHP) produced a clear neg. pattern
     by the exposure of 365 nm (10 mJ-cm-2) UV light, postbaked at 110°C for 3 min,
     and developed with a 0.3% TMAH aqueous solution
     196298-31-4P
ΙT
     RL: PRP (Properties); RCT (Reactant); SPN (Synthetic preparation)
     ; PREP (Preparation); RACT (Reactant or reagent)
        (in synthesis of calix[4]-resorcinarene dendrimer for
        photoresist material)
     196298-31-4 HCAPLUS
CN
     Pentacyclo[19.3.1.13,7.19,13.115,19]octacosa-
     1(25), 3, 5, 7(28), 9, 11, 13(27), 15, 17, 19(26), 21, 23-dodecaene,
     4,6,10,12,16,18,22,24-octakis[[3,5-bis(2-propen-1-yloxy)phenyl]methoxy]-
     2,8,14,20-tetramethyl- (CA INDEX NAME)
```

PAGE 1-A

PAGE 1-B

— CH== CH2

—— CH2— CH== CH2

PAGE 3-A

$$R2$$
 CH_2
 CH_2
 CH_2
 CH_2
 CH_2
 CH_2

PAGE 4-A

IT 65338-98-9, Calix[4]resorcinarene

RL: PRP (Properties); TEM (Technical or engineered material use); USES (Uses)

(neg.-working alkaline developable photoresists based on

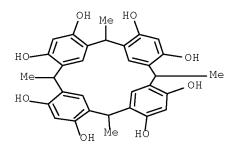
calix[4]-resorcinarene and containing crosslinker and photoacid generator)

RN 65338-98-9 HCAPLUS

CN Pentacyclo[19.3.1.13,7.19,13.115,19]octacosa-

1(25),3,5,7(28),9,11,13(27),15,17,19(26),21,23-dodecaene-

4,6,10,12,16,18,22,24-octol, 2,8,14,20-tetramethyl- (CA INDEX NAME)



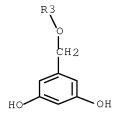
IT 196298-30-3P

RL: PRP (Properties); SPN (Synthetic preparation); TEM (Technical or engineered material use); PREP (Preparation); USES (Uses)

(neg.-working alkaline developable photoresists based on calix[4]-resorcinarene dendrimer and containing crosslinker and photoacid generator)

RN 196298-30-3 HCAPLUS

PAGE 3-A



```
CC
    74-5 (Radiation Chemistry, Photochemistry, and Photographic and Other
     Reprographic Processes)
ST
    photoresist calixarene dendrimer crosslinker photoacid generator
ΙT
    Crosslinking
        (neg.-working alkaline developable photoresists based on
        calix[4]-resorcinarene and containing crosslinker and photoacid generator)
ΙT
     Dendritic polymers
     Oligomers
     RL: PRP (Properties); RCT (Reactant); SPN (Synthetic preparation); PREP
     (Preparation); RACT (Reactant or reagent)
        (neg.-working alkaline developable photoresists based on
        calix[4]-resorcinarene dendrimer and containing crosslinker and photoacid
        generator)
     2937-59-9, 2,6-Bis(hydroxymethyl)phenol
ΙT
                                              13653-12-8,
     4,4'-Methylenebis[2,6-bis(hydroxymethyl)-phenol]
     RL: TEM (Technical or engineered material use); USES (Uses)
        (crosslinker; neq.-working alkaline developable photoresists
        based on calix[4]-resorcinarene dendrimer and containing crosslinker and
        photoacid generator)
ΙT
     75-59-2, Tetramethylammonium hydroxide
     RL: NUU (Other use, unclassified); USES (Uses)
        (developer; neg.-working alkaline developable photoresists based
        on calix[4]-resorcinarene dendrimer and containing crosslinker and
        photoacid generator)
ΙT
     13965-03-2, Bis(triphenylphosphine)palladium dichloride
     RL: CAT (Catalyst use); USES (Uses)
        (in synthesis of calix[4]-resorcinarene dendrimer for
        photoresist material)
     196298-31-4P
ΤТ
     RL: PRP (Properties); RCT (Reactant); SPN (Synthetic preparation)
     ; PREP (Preparation); RACT (Reactant or reagent)
        (in synthesis of calix[4]-resorcinarene dendrimer for
        photoresist material)
ΙT
     135710-38-2P
                    177837-80-8P
                                   182058-69-1P
     RL: RCT (Reactant); SPN (Synthetic preparation); PREP (Preparation); RACT
     (Reactant or reagent)
        (in synthesis of calix[4]-resorcinarene dendrimer for
        photoresist material)
     65338-98-9, Calix[4]resorcinarene
ΤТ
     RL: PRP (Properties); TEM (Technical or engineered material use); USES
     (Uses)
        (neg.-working alkaline developable photoresists based on
        calix[4]-resorcinarene and containing crosslinker and photoacid generator)
ΤТ
     196298-30-3P
     RL: PRP (Properties); SPN (Synthetic preparation); TEM
     (Technical or engineered material use); PREP (Preparation); USES
     (Uses)
```

10/594282 (neg.-working alkaline developable photoresists based on calix[4]-resorcinarene dendrimer and containing crosslinker and photoacid generator) ΙT 137308-86-2, Diphenyliodonium 9,10-dimethoxyanthracene-2-sulfonate RL: TEM (Technical or engineered material use); USES (Uses) (photoacid generator; neg.-working alkaline developable photoresists based on calix[4]-resorcinarene and containing crosslinker and photoacid generator) 2150-44-9, Methyl 3,5-dihydroxybenzoate ΙT RL: RCT (Reactant); RACT (Reactant or reagent) (reaction with bromopropene in synthesis of calix[4]-resorcinarene dendrimer for photoresist material) THERE ARE 12 CITED REFERENCES AVAILABLE FOR THIS REFERENCE COUNT: 12 RECORD. ALL CITATIONS AVAILABLE IN THE RE FORMAT L22 ANSWER 16 OF 20 HCAPLUS COPYRIGHT 2009 ACS on STN 1998:499270 HCAPLUS Full-text ACCESSION NUMBER: DOCUMENT NUMBER: 129:182011 ORIGINAL REFERENCE NO.: 129:36849a,36852a TITLE: Three-component negative-type photoresist based on calix[4]resorcinarene, a cross-linker, and a photoacid generator AUTHOR(S): Ueda, Mitsuru; Takahashi, Daisuke; Nakayama, Tomonari; Haba, Osamu Department of Human Sensing and Functional Sensor CORPORATE SOURCE: Engineering Graduate School of Engineering, Yamagata University, Yonezawa, Yamagata, 992-8510, Japan SOURCE: Chemistry of Materials (1998), 10(8), 2230-2234 CODEN: CMATEX; ISSN: 0897-4756 PUBLISHER: American Chemical Society DOCUMENT TYPE: Journal LANGUAGE: English A neg.-working photoresist based on calix[4]resorcinarene (C-4-RA), 4,4'methylenebis[2,6-bis(hydroxymethyl)phenol] (MBHP) as a cross-linker, and a photoacid generator diphenyliodonium 9,10-dimethoxyanthracene-2-sulfonate (DIAS) has been developed. A clear transparent film was obtained from a 25 weight% C-4-RA solution in 2-methoxyethanol. The photoresist consisting of C-4-RA (65 weight%), MBHP (25 weight%), and DIAS (10 weight%) showed a sensitivity of 4.3 mJ/cm2 and a contrast of 2.9 when it was exposed to 365 nm light and postbaked at 120° for 3 min, followed by developing with a 0.1% aqueous tetramethylammonium hydroxide solution at room temperature The mechanistic study on the formation of images is also discussed. 74708-10-4P RL: PRP (Properties); RCT (Reactant); SPN (Synthetic preparation) ; TEM (Technical or engineered material use); PREP (Preparation) ; RACT (Reactant or reagent); USES (Uses) (three-component neg.-type photoresist based on calix[4]resorcinarene, a cross-linker, and a photoacid generator)

Relative stereochemistry.

INDEX NAME)

74708-10-4 HCAPLUS

Pentacyclo[19.3.1.13,7.19,13.115,19]octacosa-

1(25),3,5,7(28),9,11,13(27),15,17,19(26),21,23-dodecaene-

RN

CN

4,6,10,12,16,18,22,24-octol, 2,8,14,20-tetramethyl-, stereoisomer (CA

IT 211577-39-8P

RL: SPN (Synthetic preparation); TEM (Technical or engineered material use); PREP (Preparation); USES (Uses) (three-component neg.-type photoresist based on

calix[4]resorcinarene, a cross-linker, and a photoacid generator)

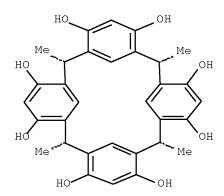
RN 211577-39-8 HCAPLUS

CN Pentacyclo[19.3.1.13,7.19,13.115,19]octacosa-1(25),3,5,7(28),9,11,13(27),15,17,19(26),21,23-dodecaene-4,6,10,12,16,18,22,24-octol, 2,8,14,20-tetramethyl-, stereoisomer, polymer with 5,5'-methylenebis[2-hydroxy-1,3-benzenedimethanol] (9CI) (CA INDEX NAME)

CM 1

CRN 74708-10-4 CMF C32 H32 O8

Relative stereochemistry.



CM 2

CRN 13653-12-8 CMF C17 H20 O6

(three-component neg.-type photoresist based on calix[4]resorcinarene, a cross-linker, and a photoacid generator)

IT 13653-12-8, 4,4'-Methylenebis[2,6-bis(hydroxymethyl)phenol] 137308-86-2, Diphenyliodonium 9,10-dimethoxyanthracene-2-sulfonate

RL: MOA (Modifier or additive use); RCT (Reactant); RACT (Reactant or reagent); USES (Uses)

(three-component neg.-type photoresist based on

calix[4]resorcinarene, a cross-linker, and a photoacid generator)

IT 74708-10-4P

RL: PRP (Properties); RCT (Reactant); SPN (Synthetic preparation); TEM (Technical or engineered material use); PRMP (Preparation)

; RACT (Reactant or reagent); USES (Uses)

(three-component neg.-type photoresist based on

calix[4]resorcinarene, a cross-linker, and a photoacid generator)

IT 211577-39-8P

RL: SPN (Synthetic preparation); TEM (Technical or engineered material use); PREP (Preparation); USES (Uses)

(three-component neg.-type photoresist based on

calix[4]resorcinarene, a cross-linker, and a photoacid generator)

REFERENCE COUNT: 16 THERE ARE 16 CITED REFERENCES AVAILABLE FOR THIS RECORD. ALL CITATIONS AVAILABLE IN THE RE FORMAT

L22 ANSWER 17 OF 20 HCAPLUS COPYRIGHT 2009 ACS on STN ACCESSION NUMBER: 1998:277408 HCAPLUS Full-text DOCUMENT NUMBER: 129:10630

ORIGINAL REFERENCE NO.: 129:2215a,2218a

TITLE: Positive-working chemical amplification-type photosensitive resin composition containing

polyphenols and method for manufacturing

resist images

INVENTOR(S): Kato, Koji; Hashimoto, Masahiro; Hashimoto, Michiaki

PATENT ASSIGNEE(S): Hitachi Chemical Co., Ltd., Japan SOURCE: Jpn. Kokai Tokkyo Koho, 8 pp.

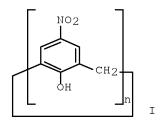
CODEN: JKXXAF

DOCUMENT TYPE: Patent LANGUAGE: Japanese

FAMILY ACC. NUM. COUNT: 1

PATENT INFORMATION:

PATENT NO.	KIND	DATE	APPLICATION NO.		DATE
				_	
JP 10115926	A	19980506	JP 1997-210284		19970805 <
PRIORITY APPLN. INFO.:			JP 1996-221938	А	19960823 <
OTHER SOURCE(S):	MARPAT	129:10630			
GI					



AB A pos.-type chemical amplification-series photosensitive resin composition contains (a) a resin soluble in aqueous alkali solution, (b) polynitrophenols (calixarene) (I; n = 4-8), (c) a compound generating an acid upon irradiation with active chemical ray, and (d) a compound possessing on the side chain, a group decomposable by acid which increases solubility in aqueous alkali solution by acid-catalyzed reaction. The content of low-mol. weight component having mol. weight ≤2,000 as polystyrene in the above composition is ≤10 weight%. Also claimed is a method for preparing resist images, in which the coating of above resin composition is irradiated with active chemical ray and then developed. The composition provides resist patterns of good resolution and shows high sensitivity, high degree of resolution, and high heat resistance and is used for microprocessing of semiconductor devices.

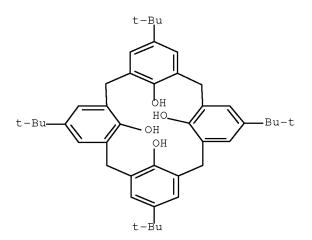
IT 60705-62-6F

RL: RCT (Reactant); SPN (Synthetic preparation); PREP (Preparation); RACT (Reactant or reagent)

(pos.-working chemical amplification-type photosensitive resin composition containing polyphenols and method for manufacturing $x \in sist$ images)

RN 60705-62-6 HCAPLUS

CN Pentacyclo[19.3.1.13,7.19,13.115,19]octacosa-1(25),3,5,7(28),9,11,13(27),15,17,19(26),21,23-dodecaene-25,26,27,28tetrol, 5,11,17,23-tetrakis(1,1-dimethylethyl)- (CA INDEX NAME)



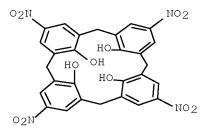
IT 109051-62-9P

RL: SPN (Synthetic preparation); TEM (Technical or engineered material use); PREP (Preparation); USES (Uses)

(pos.-working chemical amplification-type photosensitive resin composition containing polyphenols and method for manufacturing resist images)

RN 109051-62-9 HCAPLUS

CN Pentacyclo[19.3.1.13,7.19,13.115,19]octacosa-1(25),3,5,7(28),9,11,13(27),15,17,19(26),21,23-dodecaene-25,26,27,28tetrol, 5,11,17,23-tetranitro- (CA INDEX NAME)



IC ICM G03F007-039

ICS G03F007-004; H01L021-027

CC 74-5 (Radiation Chemistry, Photochemistry, and Photographic and Other Reprographic Processes)

ST pos working photoresist alkali sol; semiconductor device manuf photoresist; polyphenol photoresist chem amplification photoresist; calixarene pos working photoresist

IT Phenolic resins, preparation

RL: SPN (Synthetic preparation); TEM (Technical or engineered material use); PREP (Preparation); USES (Uses)

(novolak; pos.-working chemical amplification-type photosensitive resin composition containing polyphenols and method for manufacturing resist images)

IT Positive photoresists

Semiconductor devices

(pos.-working chemical amplification-type photosensitive resin composition containing polyphenols and method for manufacturing resist images)

IT Metacyclophanes

RL: SPN (Synthetic preparation); TEM (Technical or engineered material use); PREP (Preparation); USES (Uses)

(pos.-working chemical amplification-type photosensitive resin composition containing polyphenols and method for manufacturing resist images)

IT 50-00-0, Formaldehyde, reactions 98-54-4 24979-70-2, Poly(p-vinylphenol)

RL: RCT (Reactant); RACT (Reactant or reagent)

(pos.-working chemical amplification-type photosensitive resin composition containing polyphenols and method for manufacturing resist images)

IT 60705-62-6P 68971-82-4P

RL: RCT (Reactant); SPN (Synthetic preparation); PREP

(Preparation); RACT (Reactant or reagent)

(pos.-working chemical amplification-type photosensitive resin composition containing polyphenols and method for manufacturing resist images)

IT 24979-70-2DP, Poly(p-vinylphenol), tetrahydropyranyl-substituted 27029-76-1P, m-Cresol-p-cresol-formalin copolymer 60288-40-6P, Trimethylsulfonium trifluoromethanesulfonate 109051-62-9P 109081-46-1P

RL: SPN (Synthetic preparation); TEM (Technical or engineered material use); PREP (Preparation); USES (Uses)

(pos.-working chemical amplification-type photosensitive resin composition

containing polyphenols and method for manufacturing resist images)

IT 9016-83-5, CN 19

RL: TEM (Technical or engineered material use); USES (Uses)
(pos.-working chemical amplification-type photosensitive resin composition containing polyphenols and method for manufacturing resist images)

L22 ANSWER 18 OF 20 HCAPLUS COPYRIGHT 2009 ACS on STN ACCESSION NUMBER: 1997:582349 HCAPLUS Full-text

DOCUMENT NUMBER: 127:270381

ORIGINAL REFERENCE NO.: 127:52641a,52644a

TITLE: A positive-working alkaline developable

photoresist based on benzylether dendrimer and

a dissolution inhibitor

AUTHOR(S): Haba, Osamu; Haga, Kohji; Ueda, Mitsuru

CORPORATE SOURCE: Department of Human Sensing and Functional Sensor

engineering, Graduate School of Engineering, Yamagata

University, Yonezawa, 992, Japan

SOURCE: Polymeric Materials Science and Engineering (

1997), 77, 426-427

CODEN: PMSEDG; ISSN: 0743-0515

PUBLISHER: American Chemical Society

DOCUMENT TYPE: Journal LANGUAGE: English

Dendrimers are polymers with a new mol. architecture, which is characterized by possessing central poly-functional core, from which arise successive layers of monomer units with a branch occurring at each monomer unit. They are monodisperse materials as well as the calixarene, and their mol. weight reaches ten thousands as well as the novolak resin. Thus the dendrimers are promising material for high sensitive photoresists. We designed a new dendrimer which contains phenol groups in the exterior to be soluble in aqueous alkaline solution and calix[4]resorcinarene in the interior to increase the number of the phenol group even in the lower generation. We now report new pos.-working alkaline developable photoresist based on this dendrimer.

IT 196298-31-4P

RL: PNU (Preparation, unclassified); RCT (Reactant); PREP (Preparation); RACT (Reactant or reagent)

(pos.-working alkaline developable photoresist based on benzyl-ether dendrimer and dissoln. inhibitor)

RN 196298-31-4 HCAPLUS

CN Pentacyclo[19.3.1.13,7.19,13.115,19]octacosa-1(25),3,5,7(28),9,11,13(27),15,17,19(26),21,23-dodecaene, 4,6,10,12,16,18,22,24-octakis[[3,5-bis(2-propen-1-yloxy)phenyl]methoxy]-2,8,14,20-tetramethyl- (CA INDEX NAME)

PAGE 1-A

PAGE 1-B

— CH== CH2

—— CH2— CH== CH2

PAGE 3-A

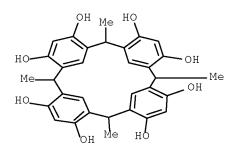
PAGE 4-A

IT 65338-98-9, Calix[4]resorcinarene

RL: RCT (Reactant); RACT (Reactant or reagent) (pos.-working alkaline developable photoresist based on benzyl-ether dendrimer and dissoln. inhibitor)

RN 65338-98-9 HCAPLUS

CN Pentacyclo[19.3.1.13,7.19,13.115,19]octacosa-1(25),3,5,7(28),9,11,13(27),15,17,19(26),21,23-dodecaene-4,6,10,12,16,18,22,24-octol, 2,8,14,20-tetramethyl- (CA INDEX NAME)



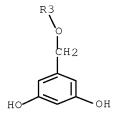
IT 196298-30-3P

RL: SPN (Synthetic preparation); TEM (Technical or engineered material use); PREP (Preparation); USES (Uses) (pos.-working alkaline developable photoresist based on benzyl-ether dendrimer and dissoln. inhibitor)

PAGE 1-A

RN 196298-30-3 HCAPLUS
CN 1,3-Benzenediol, 5,5',5'',5''',5'''',5'''',5''''',5''''',5'''''-[(2,8,14,20-tetramethylpentacyclo[19.3.1.13,7.19,13.115,19]octacosa-1(25),3,5,7(28),9,11,13(27),15,17,19(26),21,23-dodecaene-4,6,10,12,16,18,22,24-octayl)octakis(oxymethylene)]octakis-(9CI) (CA INDEX NAME)

PAGE 3-A



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CC
     74-5 (Radiation Chemistry, Photochemistry, and Photographic and Other
     Reprographic Processes)
ST
     pos alk developable photoresist benzylether dendrimer
ΙT
     Photoresists
        (pos.-working alkaline developable photoresist based on
        benzyl-ether dendrimer and dissoln. inhibitor)
ΙT
     Dendritic polymers
     RL: TEM (Technical or engineered material use); USES (Uses)
        (pos.-working alkaline developable photoresist based on
        benzyl-ether dendrimer and dissoln. inhibitor)
ΙT
     84522-08-7, 2,3,4-Tris(1-oxo-2-diazonaphthoquinone-4-
     sulfonyloxy) benzophenone
     RL: TEM (Technical or engineered material use); USES (Uses)
        (dissoln. inhibitor; pos.-working alkaline developable photoresist
        based on benzyl-ether dendrimer and dissoln. inhibitor)
                  177837-80-8
ΙT
     135710-38-2
                                182058-69-1
     RL: FMU (Formation, unclassified); RCT (Reactant); FORM (Formation,
     nonpreparative); RACT (Reactant or reagent)
        (pos.-working alkaline developable photoresist based on
        benzyl-ether dendrimer and dissoln. inhibitor)
     67-64-1, 2-Propanone, uses 75-59-2, Tetramethylammonium hydroxide
ΙT
     109-99-9, THF, uses 111-96-6, Bis(2-methoxyethyl)ether 123-91-1,
     1,4-Dioxane, uses
     RL: NUU (Other use, unclassified); USES (Uses)
        (pos.-working alkaline developable photoresist based on
        benzyl-ether dendrimer and dissoln. inhibitor)
     196298-31-4P
ΙT
     RL: PNU (Preparation, unclassified); RCT (Reactant); PREP
     (Preparation); RACT (Reactant or reagent)
        (pos.-working alkaline developable photoresist based on
        benzyl-ether dendrimer and dissoln. inhibitor)
     106-95-6, 3-Bromopropene, reactions 540-69-2, Ammonium formate
ΤТ
     558-13-4, Carbon bromide (CBr4)
                                      584-08-7, Potassium carbonate (K2CO3)
     603-35-0, Triphenylphosphine, reactions 2150-44-9,
                                   7681-82-5, Sodium iodide (NaI), reactions
     Methyl-3,5-dihydroxy-benzoate
     13965-03-2, Bis(triphenylphosphine)palladium dichloride 16853-85-3
     17455-13-9, 1,4,7,10,13,16-Hexaoxacyclooctadecane
                                                         53208-22-3,
     Diazonaphthoquinone 65338-98-9, Calix[4]resorcinarene
     RL: RCT (Reactant); RACT (Reactant or reagent)
        (pos.-working alkaline developable photoresist based on
        benzyl-ether dendrimer and dissoln. inhibitor)
     196298-30-3P
ΙT
     RL: SPN (Synthetic preparation); TEM (Technical or engineered
     material use); PREP (Preparation); USES (Uses)
```

(pos.-working alkaline developable photoresist based on

benzyl-ether dendrimer and dissoln. inhibitor)

L22 ANSWER 19 OF 20 HCAPLUS COPYRIGHT 2009 ACS on STN ACCESSION NUMBER: 1994:334992 HCAPLUS Full-text

DOCUMENT NUMBER: 120:334992

ORIGINAL REFERENCE NO.: 120:58693a,58696a

TITLE: Photosensitive resin composition and resist

image formation

INVENTOR(S): Kato, Koji; Kasuya, Kei; Isobe, Asao

PATENT ASSIGNEE(S): Hitachi Chemical Co Ltd, Japan SOURCE: Jpn. Kokai Tokkyo Koho, 9 pp.

CODEN: JKXXAF

DOCUMENT TYPE: Patent LANGUAGE: Japanese

FAMILY ACC. NUM. COUNT: 1

PATENT INFORMATION:

PATENT NO.	KIND	DATE	APPLICATION NO.	DATE
JP 05346664	A	19931227	JP 1992-154911	19920615 <
PRIORITY APPLN. INFO.:			JP 1992-154911	19920615 <

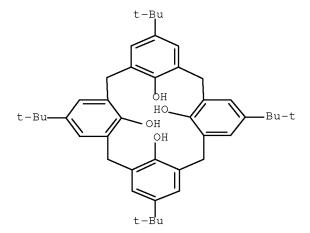
GI For diagram(s), see printed CA Issue.

AB The composition comprises alkali-soluble novolak resin containing 0-10 weight% low mol. weight composition with mol. weight ≤2000 (as polystyrene), a quinonediazide compound, and phenolic cyclic compound I (n = 4-8). The composition is coated, exposed, and developed to form images. The composition shows high sensitivity, resolution, thermal-resistance, and suitable for pos-working resist for integrated circuits.

IT 60705-62-6P

RN 60705-62-6 HCAPLUS

CN Pentacyclo[19.3.1.13,7.19,13.115,19]octacosa-1(25),3,5,7(28),9,11,13(27),15,17,19(26),21,23-dodecaene-25,26,27,28tetrol, 5,11,17,23-tetrakis(1,1-dimethylethyl)- (CA INDEX NAME)



IT 109051-62-9P

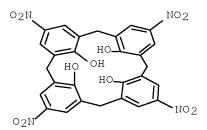
RL: PREP (Preparation)

(preparation of, pos.-working photoresist containing)

RN 109051-62-9 HCAPLUS

CN Pentacyclo[19.3.1.13,7.19,13.115,19]octacosa-

1(25),3,5,7(28),9,11,13(27),15,17,19(26),21,23-dodecaene-25,26,27,28-tetrol, 5,11,17,23-tetranitro- (CA INDEX NAME)



IC ICM G03F007-022

ICS G03F007-023; G03F007-30; H01L021-027

CC 74-5 (Radiation Chemistry, Photochemistry, and Photographic and Other Reprographic Processes)

Section cross-reference(s): 76

ST resist cyclic phenol compd; quinonediazide novolak resin resist

IT Phenolic resins, uses

RL: USES (Uses)

(novolak, pos.-working photoresist containing)

IT Resists

(photo-, containing novolak resin and quinonediazide compound and cyclic phenol derivative)

IT 27029-76-1, m-Cresol-p-cresol-formaldehyde copolymer 100346-90-5, m-Cresol-p-cresol-formaldehyde-2,5-xylenol copolymer 112504-03-7, m-Cresol-p-cresol-formaldehyde-3,5-xylenol copolymer

RL: USES (Uses)

(pos.-working photoresist containing)

IT 60705-62-6P 68971-82-4P

RL: RCT (Reactant); SPN (Synthetic preparation); PREP (Preparation); RACT (Reactant or reagent)

(preparation and nitration of)

IT 109051-62-9P 109081-46-1P

RL: PREP (Preparation)

(preparation of, pos.-working photoresist containing)

L22 ANSWER 20 OF 20 HCAPLUS COPYRIGHT 2009 ACS on STN ACCESSION NUMBER: 1992:560915 HCAPLUS Full-text

DOCUMENT NUMBER: 117:160915

ORIGINAL REFERENCE NO.: 117:27633a,27636a

TITLE: Positive-working photoresist composition INVENTOR(S): Kawabe, Yasumasa; Tan, Shiro; Kuboyama, Reiko

PATENT ASSIGNEE(S): Fuji Photo Film Co., Ltd., Japan SOURCE: Jpn. Kokai Tokkyo Koho, 10 pp.

CODEN: JKXXAF

DOCUMENT TYPE: Patent LANGUAGE: Japanese

FAMILY ACC. NUM. COUNT: 1

PATENT INFORMATION:

PATENT NO.	KIND	DATE	APPLICATION NO.	DATE
JP 03279957	A	19911211	JP 1990-80027	19900328 <

PRIORITY APPLN. INFO.:

JP 1990-80027

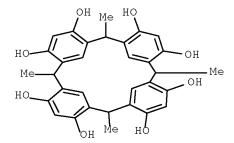
19900328 <--

- GI For diagram(s), see printed CA Issue.
- The title pos.-working photoresist composition contains the 1,2-naphthoquinonediazido-5-(and/or-4-) sulfonic acid ester of the polyhydric compds., (I; R1 R4 = H, OH, halo, alkyl, aryl, aralkyl, alkoxy, alkenyl, aryl, alkoxycarbonyl, CN, NO2; ≥1 of R2 R4 is OH; R5, R6 = H, alkyl, aryl; X = single bond or OCH2; n = 3-8) or (II; R7 R10 = same as R1 R4 above; ≥ of R7 R10 in OH; R11, R12 = H, alkyl, aryl; X = single bond, OCH2; n = 3-8) and an alkali-soluble resin. The photoresist has high sensitivity and give high resolution patterns.
- IT 65338-98-9P

RL: RCT (Reactant); SPN (Synthetic preparation); PREP (Preparation); RACT (Reactant or reagent)

(preparation and reaction of, in preparation of photoresist component)

- RN 65338-98-9 HCAPLUS
- CN Pentacyclo[19.3.1.13,7.19,13.115,19]octacosa-1(25),3,5,7(28),9,11,13(27),15,17,19(26),21,23-dodecaene-4,6,10,12,16,18,22,24-octol, 2,8,14,20-tetramethyl- (CA INDEX NAME)



IC ICM G03F007-022

ICS H01L021-027

- CC 74-5 (Radiation Chemistry, Photochemistry, and Photographic and Other Reprographic Processes)
 Section cross-reference(s): 76
- ST pos photoresist naphthoquinodiazidosulfonate
- IT Semiconductor devices

(fabrication of, high resolution photoresist for)

IT Resists

(photo-, containing naphthaquinonediazidosulfonic acid ester, pos.-working)

IT 1506-76-9P 65338-98-9P

RL: RCT (Reactant); SPN (Synthetic preparation); PREP

(Preparation); RACT (Reactant or reagent)

(preparation and reaction of, in preparation of photoresist component)

- IT 143637-17-6P
 - RL: PREP (Preparation)

(preparation of, as photoresist component)

IT 143637-35-8P

RL: PREP (Preparation)

(preparation of, photoresist composition containing)

***** SEARCH HISTORY *****

=> d his nof

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FILE 'REGISTRY' ENTERED AT 11:22:42 ON 19 MAY 2009

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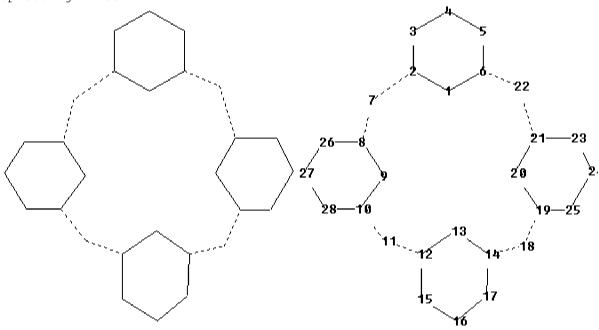
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STRUCTURE UPLOADED

D

Uploading L2.str



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12-13 12-15 13-14 14-17 14-18 15-16 16-17 18-19 19-20 19-25 20-21 21-22
21-23 23-24
24-25 26-27 27-28
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containing 1:
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22:Atom 23:Atom 24:Atom 25:Atom 26:Atom 27:Atom 28:Atom

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L5
         17874 SEA SSS FUL L3
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                D RN
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L11
           3317 SEA ABB=ON PLU=ON L9 (L) PREP+ALL/RL 3706 SEA ABB=ON PLU=ON L9 (L) RACT/RL
L12
L13
L14
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chain bonds :
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2-3 3-4 4-5 5-6 5-7 8-9 9-10 10-11 11-16 11-17
exact bonds :
1-2 1-8
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Saturation
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9:

Saturation : Unsaturated

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		D QUE L22
		D L22 1-20 IBIB ABS HITSTR HITIND